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Author Index

- Abe, Y., and H. Okuhira, ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates 203–204 (2003) 175
- Abe, Y., M. Komatsu and H. Okuhira, Estimation of ToF-SIMS information depth in micro-corrosion analysis 203–204 (2003) 859
- Adams, F., see Belykh, S.F. 203–204 (2003) 122
- Adams, F., see Belykh, S.F. 203–204 (2003) 126
- Adriaens, A., see Belykh, S.F. 203–204 (2003) 122
- Adriaens, A., see Belykh, S.F. 203–204 (2003) 126
- Aguilar, M., see Guzmán, B. 203–204 (2003) 139
- Alexandrov, O.V., D.Yu. Kazantsev and A.P. Kovarsky, Direct determination of p/n junction depth by the emission of matrix complex ions 203–204 (2003) 520
- Al-Harhi, S.H., see Dowsett, M.G. 203–204 (2003) 363
- Alibhai, A.A., R.J. Chater, D.S. McPhail and B.A. Shollock, Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys 203–204 (2003) 630
- Allara, D.L., see Haynie, B.C. 203–204 (2003) 433
- Amemiya, T., H. Gong, K. Takaya, M. Tozu and Y. Ohashi, Changes of vitamins A and E in the rat retina under light and dark conditions detected with TOF-SIMS 203–204 (2003) 738
- Amemiya, T., see Gong, H. 203–204 (2003) 734
- Amemiya, T., see Kinoshita, A. 203–204 (2003) 742
- Ameziane, O., see Guzmán, B. 203–204 (2003) 139
- Anderle, M., see Bersani, M. 203–204 (2003) 281
- Anderle, M., see Lazzeri, P. 203–204 (2003) 767
- Aoki, T., see Toyoda, N. 203–204 (2003) 214
- Arlinghaus, H.F., M. Ostrop, O. Friedrichs and J.C. Feldner, Genome diagnostics with TOF-SIMS 203–204 (2003) 689
- Arlinghaus, H.F., see Fartmann, M. 203–204 (2003) 726
- Arlinghaus, H.F., see Feldner, J.C. 203–204 (2003) 722
- Arlinghaus, H.F., see Vering, G. 203–204 (2003) 785
- Asomoza, R., see Villegas, A. 203–204 (2003) 94
- Aubriet, F., C. Poleunis and P. Bertrand, Investigation of the cluster ion formation process for inorganic compounds in static SIMS 203–204 (2003) 114
- Aubriet, F., C. Poleunis and P. Bertrand, Effects of sample preparation on ion yield in the study of inorganic salts by s-SIMS 203–204 (2003) 180
- Audinot, J.-N., M. Yegles, A. Labarthe, D. Ruch, R. Wennig and H.-N. Migeon, Detection and quantification of benzodiazepines in hair by ToF-SIMS: preliminary results 203–204 (2003) 718
- Auditore, A., see Licciardello, A. 203–204 (2003) 556
- Auditore, A., see Médard, N. 203–204 (2003) 571
- Augustus, P., see Dowsett, M.G. 203–204 (2003) 273
- Augustus, P., see Kelly, J.H. 203–204 (2003) 260
- Baborowski, J., see Coullerez, G. 203–204 (2003) 527
- Baboux, N., see Laugier, F. 203–204 (2003) 348
- Bailey, P., see Dowsett, M.G. 203–204 (2003) 363
- Ballutaud, D., see Jomard, F. 203–204 (2003) 478
- Barcz, A., M. Zielinski, E. Nossarzewska and G. Lindstroem, Extremely deep SIMS profiling: oxygen in FZ silicon 203–204 (2003) 396
- Barozzi, M., see Bersani, M. 203–204 (2003) 281
- Beanland, R., see Dowsett, M.G. 203–204 (2003) 273
- Beanland, R., see Kelly, J.H. 203–204 (2003) 260
- Bekkerman, A.D., see Dzhemilev, N.Kh. 203–204 (2003) 118
- Bellingham, J., and M.G. Dowsett, The energy spectra of secondary ions sputtered from Si and SiGe by ultra-low-energy primary ions 203–204 (2003) 130
- Bellingham, J., M.G. Dowsett, E. Collart and D. Kirkwood, Quantitative analysis of the top 5 nm of boron ultra-shallow implants 203–204 (2003) 851
- Belykh, S.F., A.P. Kovarsky, V.V. Palitsin, A. Adriaens and F. Adams, Features of non-additive sputtering for various “molecular projectile–solid” systems 203–204 (2003) 122
- Belykh, S.F., V.V. Palitsin, A. Adriaens and F. Adams, Effect of the projectile parameters on the charge state formation process in solid sputtering 203–204 (2003) 126
- Bennett, J., C. Gondran, C. Sparks, P.Y. Hung and A. Hou, SIMS depth profiling of advanced gate dielectric materials 203–204 (2003) 409
- Bennett, J., see van der Heide, P.A.W. 203–204 (2003) 156
- Bennett, J., see van der Heide, P.A.W. 203–204 (2003) 306
- Benninghoven, A., Foreword 203–204 (2003) 1
- Benninghoven, A., see Kollmer, F. 203–204 (2003) 238
- Benninghoven, A., see Médard, N. 203–204 (2003) 571
- Benninghoven, A., see Xin, G. 203–204 (2003) 441
- Bergmaier, A., see Vandervorst, W. 203–204 (2003) 371

- Bersani, M., D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo, D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides 203-204 (2003) 281
- Bersani, M., see Lazzeri, P. 203-204 (2003) 445
- Bertrand, P., A. Delcorte and B.J. Garrison, Molecular SIMS for organic layers: new insights 203-204 (2003) 160
- Bertrand, P., see Aubriet, F. 203-204 (2003) 114
- Bertrand, P., see Aubriet, F. 203-204 (2003) 180
- Bertrand, P., see Delcorte, A. 203-204 (2003) 106
- Bertrand, P., see Delcorte, A. 203-204 (2003) 166
- Bertrand, P., see Houssiau, L. 203-204 (2003) 580
- Bertrand, P., see Médard, N. 203-204 (2003) 571
- Bertrand, P., see Poleunis, C. 203-204 (2003) 693
- Bertrand, P., see Wojciechowski, I. 203-204 (2003) 102
- Besling, W., see Conard, T. 203-204 (2003) 400
- Bexell, U., P. Carlsson and M. Olsson, Tribological characterisation of an organic coating by the use of ToF-SIMS 203-204 (2003) 596
- Bijma, J., see Vering, G. 203-204 (2003) 785
- Blanco, J.M., see Guzmán, B. 203-204 (2003) 139
- Blenkinsopp, P., see Davies, N. 203-204 (2003) 223
- Blenkinsopp, P., see Gibbons, R. 203-204 (2003) 343
- Blenkinsopp, P., see Wong, S.C.C. 203-204 (2003) 219
- Boes, C., see Ruch, D. 203-204 (2003) 566
- Borchardt, G., see Fielitz, P. 203-204 (2003) 639
- Borchardt, G., see Weber, S. 203-204 (2003) 656
- Bourdos, N., see Kollmer, F. 203-204 (2003) 238
- Braun, R.M., see Xu, J.Y. 203-204 (2003) 201
- Brazzelli, D., see Zanderigo, F. 203-204 (2003) 437
- Brijs, B., see Huyghebaert, C. 203-204 (2003) 56
- Brijs, B., see Huyghebaert, C. 203-204 (2003) 134
- Brongersma, H.H., see Janssens, T. 203-204 (2003) 30
- Brox, O., see Xin, G. 203-204 (2003) 441
- Bulle-Lieuwma, C.W.T., W.J.H. van Gennip, J.K.J. van Duren, P. Jonkheijm, R.A.J. Janssen and J.W. Niemantsverdriet, Characterization of polymer solar cells by TOF-SIMS depth profiling 203-204 (2003) 547
- Carlsson, P., see Bexell, U. 203-204 (2003) 596
- Castner, D.G., see Wagner, M.S. 203-204 (2003) 698
- Castner, D.G., see Wagner, M.S. 203-204 (2003) 704
- Caymax, M., see Vandervorst, W. 203-204 (2003) 371
- Chan, C.-M., see Weng, L.T. 203-204 (2003) 532
- Chandra, S., SIMS ion microscopy as a novel, practical tool for subcellular chemical imaging in cancer research 203-204 (2003) 679
- Chang, H.S., see Shon, H.K. 203-204 (2003) 423
- Chater, R.J., see Alibhai, A.A. 203-204 (2003) 630
- Chater, R.J., see Hallett, K. 203-204 (2003) 789
- Chen, C.Y., Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng, Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users 203-204 (2003) 461
- Chen, C.Y., Y.C. Ling, J.T. Wang and H.Y. Chen, SIMS depth profiling analysis of electrical arc residues in fire investigation 203-204 (2003) 779
- Chen, H.Y., see Chen, C.Y. 203-204 (2003) 779
- Chevolot, Y., see Coullerez, G. 203-204 (2003) 527
- Chiang, C.I., see Chiou, C.Y. 203-204 (2003) 482
- Chiou, C.Y., C.C. Wang, Y.C. Ling and C.I. Chiang, Secondary ion mass spectrometry analysis of In-doped p-type GaN films 203-204 (2003) 482
- Cho, S.B., H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon, Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration 203-204 (2003) 302
- Chou, P.-F., see Dowsett, M.G. 203-204 (2003) 500
- Chrysoulis, S.L., see Dimov, S.S. 203-204 (2003) 235
- Chrysoulis, S.L., see Dimov, S.S. 203-204 (2003) 644
- Chun, H., see Lee, Y. 203-204 (2003) 875
- Claesson, Å., see Hellsing, M. 203-204 (2003) 648
- Clauser, G., see Lazzeri, P. 203-204 (2003) 767
- Cliff, B., D.E. Weibel, N.P. Lockyer, H. Jungnickel, G. Stephens and J.C. Vickerman, Detection of chlorinated pesticides on the surface of fungus using ToF-SIMS 203-204 (2003) 710
- Cliff, B., N.P. Lockyer, C. Corlett and J.C. Vickerman, Development of instrumentation for routine ToF-SIMS imaging analysis of biological material 203-204 (2003) 730
- Collart, E., see Bellingham, J. 203-204 (2003) 851
- Compère, C., see Poleunis, C. 203-204 (2003) 693
- Conard, T., see De Witte, H. 203-204 (2003) 523
- Conard, T., W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard, TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films 203-204 (2003) 400
- Cooke, G.A., see Dowsett, M.G. 203-204 (2003) 500
- Corcoran, S.F., see Dowsett, M.G. 203-204 (2003) 500
- Corlett, C., see Cliff, B. 203-204 (2003) 730
- Coullerez, G., J. Baborowski, C. Viornery, Y. Chevolot, N. Xanthopoulos, N. Ledermann, P. Muralt, N. Setter and H.J. Mathieu, Imaging by time-of-flight secondary ion mass spectrometry of plasma patterned metal and oxide thin films 203-204 (2003) 527
- Coullerez, G., S. Lundmark, M. Malkoch, H. Magnusson, E. Malmström, A. Hult and H.J. Mathieu, Insights into ToF-SIMS analysis of dendritic macromolecules: cationization and PCA to probe their molecular weight on surfaces 203-204 (2003) 620
- Crivelli, B., see Bersani, M. 203-204 (2003) 281
- Crone, C., see Vering, G. 203-204 (2003) 785
- Cubaynes, F.N., see van Berkum, J.G.M. 203-204 (2003) 414
- Dambach, S., see Fartmann, M. 203-204 (2003) 726

- Davies, N., D.E. Weibel, P. Blenkinsopp, N. Lockyer, R. Hill and J.C. Vickerman, Development and experimental application of a gold liquid metal ion source 203-204 (2003) 223
- De Chambost, E., P. Monsallut, B. Rasser and M. Schuhmacher, Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique 203-204 (2003) 391
- de Chambost, E., see Hombourger, C. 203-204 (2003) 383
- De Witte, H., T. Conard, W. Vandervorst and R. Gijbels, Ion-bombardment artifact in TOF-SIMS analysis of ZrO₂/SiO₂/Si stacks 203-204 (2003) 523
- Delcorte, A., I. Wojciechowski, X. Gonze, B.J. Garrison and P. Bertrand, The formation of singly and doubly cationized oligomers in SIMS 203-204 (2003) 106
- Delcorte, A., P. Bertrand and B.J. Garrison, A microscopic view of organic sample sputtering 203-204 (2003) 166
- Delcorte, A., see Bertrand, P. 203-204 (2003) 160
- Delcorte, A., see Garrison, B.J. 203-204 (2003) 67
- Delcorte, A., see Wojciechowski, I. 203-204 (2003) 102
- Deng, R.C., see Chen, C.Y. 203-204 (2003) 461
- Desgranges, L., see Rasser, B. 203-204 (2003) 673
- Desse, F., see Hombourger, C. 203-204 (2003) 383
- Dimov, S.S., and S.L. Chrysosoulis, Trace element analysis of precious metals in minerals by time-of-flight resonance ionization mass spectrometry 203-204 (2003) 235
- Dimov, S.S., S.L. Chrysosoulis and R.N. Sodhi, Speciation of surface gold in pressure oxidized carbonaceous gold ores by TOF-SIMS and TOF-LIMS 203-204 (2003) 644
- Dollinger, G., see Vandervorst, W. 203-204 (2003) 371
- Dong, G., see Xin, G. 203-204 (2003) 441
- Douglas, M., see Li-Fatou, A.V. 203-204 (2003) 290
- Dowsett, M.G., Depth profiling using ultra-low-energy secondary ion mass spectrometry 203-204 (2003) 5
- Dowsett, M.G., J.H. Kelly, G. Rowlands, T.J. Ormsby, B. Guzmán, P. Augustus and R. Beanland, On determining accurate positions, separations, and internal profiles for delta layers 203-204 (2003) 273
- Dowsett, M.G., R. Morris, P.-F. Chou, S.F. Corcoran, H. Kheyandish, G.A. Cooke, J.L. Maul and S.B. Patel, Charge compensation using optical conductivity enhancement and simple analytical protocols for SIMS of resistive Si_{1-x}Ge_x alloy layers 203-204 (2003) 500
- Dowsett, M.G., see Bellingham, J. 203-204 (2003) 130
- Dowsett, M.G., see Bellingham, J. 203-204 (2003) 851
- Dowsett, M.G., see Gard, F.S. 203-204 (2003) 490
- Dowsett, M.G., see Gibbons, R. 203-204 (2003) 343
- Dowsett, M.G., see Kelly, J.H. 203-204 (2003) 260
- Dowsett, M.G., see Rees, E.E. 203-204 (2003) 660
- Dowsett, M.G., T.J. Ormsby, F.S. Gard, S.H. Al-Harhi, B. Guzmán, C.F. McConville, T.C.Q. Noakes and P. Bailey, Determination of the variation in sputter yield in the SIMS transient region using MEIS 203-204 (2003) 363
- Duc, T.M., see Médard, N. 203-204 (2003) 571
- Dupuy, J.C., see Laugier, F. 203-204 (2003) 348
- Dzhemilev, N.Kh., A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev, The unimolecular decay of Al_n[±] and Si_n[±] sputtered clusters 203-204 (2003) 118
- Efremov, A.A., see Krüger, D. 203-204 (2003) 285
- Elacob, E., see Bersani, M. 203-204 (2003) 281
- Esaulov, V.A., see Staicu-Casagrande, E.M. 203-204 (2003) 86
- Fahey, A., see Gillen, G. 203-204 (2003) 209
- Fahey, A., see Roberson, S. 203-204 (2003) 855
- Fanciulli, M., see Ferrari, S. 203-204 (2003) 52
- Fanciulli, M., see Perego, M. 203-204 (2003) 110
- Fartmann, M., S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus, Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS 203-204 (2003) 726
- Feldner, J.C., M. Ostrop, O. Friedrichs, S. Sohn, D. Lipinsky, U. Gunst and H.F. Arlinghaus, TOF-SIMS investigation of the immobilization process of peptide nucleic acids 203-204 (2003) 722
- Feldner, J.C., see Arlinghaus, H.F. 203-204 (2003) 689
- Fenner, D.B., see Toyoda, N. 203-204 (2003) 214
- Ferrari, S., M. Perego and M. Fanciulli, Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs⁺ sputtering in negative mode by ToF-SIMS: a full spectrum approach 203-204 (2003) 52
- Ferrari, S., see Perego, M. 203-204 (2003) 110
- Fielitz, P., G. Borchardt, M. Schmücker, H. Schneider and P. Willich, Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling 203-204 (2003) 639
- Fokine, M., see Hellsing, M. 203-204 (2003) 648
- Franco, G., see Lazzeri, P. 203-204 (2003) 445
- Franzreb, K., and P. Williams, Mass-resolved low-energy back-scattering of alkali ions 203-204 (2003) 98
- Franzreb, K., P. Williams, J. Lörinčík and Z. Šroubek, Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O₂⁺ bombardment 203-204 (2003) 39
- Friedrich, J., see Gross, Th. 203-204 (2003) 575
- Friedrichs, O., see Arlinghaus, H.F. 203-204 (2003) 689
- Friedrichs, O., see Feldner, J.C. 203-204 (2003) 722
- Frühau, J., see Vandervorst, W. 203-204 (2003) 371
- Fujiyama, N., A. Karen, D.B. Sams, R.S. Hockett, K. Shingu and N. Inoue, SIMS

- quantification of low concentration of nitrogen doped in silicon crystals 203-204 (2003) 457
- Fujiyama, N., see Yamada, K. 203-204 (2003) 512
- Fukui, Y., see Nishi, A. 203-204 (2003) 470
- Gard, F.S., J.D. Riley, M.G. Dowsett and K. Prince, The effect of Se and Zn predeposition on thermal diffusion of elements across the ZnSe/GaAs interface studied by SIMS 203-204 (2003) 490
- Gard, F.S., see Dowsett, M.G. 203-204 (2003) 363
- Garozzo, M., see Lazzeri, P. 203-204 (2003) 445
- Garrison, B.J., A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd, Big molecule ejection—SIMS vs. MALDI 203-204 (2003) 67
- Garrison, B.J., see Bertrand, P. 203-204 (2003) 160
- Garrison, B.J., see Delcorte, A. 203-204 (2003) 106
- Garrison, B.J., see Delcorte, A. 203-204 (2003) 166
- Garrison, B.J., see Medvedeva, M. 203-204 (2003) 148
- Geppert, T., see Maier, M. 203-204 (2003) 486
- Gerardi, C., see Lazzeri, P. 203-204 (2003) 445
- Geuens, I., see Lenaerts, J. 203-204 (2003) 614
- Gibbons, R., M.G. Dowsett, J. Kelly, P. Blenkinsopp, R. Hill, D. Richards and N. Loibl, A floating low energy electron gun (FLEG) for charge compensation in SIMS and other applications 203-204 (2003) 343
- Gijbels, R., see De Witte, H. 203-204 (2003) 523
- Gijbels, R., see Lenaerts, J. 203-204 (2003) 614
- Gildenpfennig, A., see Janssens, T. 203-204 (2003) 30
- Gillen, G., and A. Fahey, Secondary ion mass spectrometry using cluster primary ion beams 203-204 (2003) 209
- Gilmore, I.S., and M.P. Seah, G-SIMS of crystallisable organics 203-204 (2003) 551
- Gilmore, I.S., and M.P. Seah, Investigating the difficulty of eliminating flood gun damage in TOF-SIMS 203-204 (2003) 600
- Giubertoni, D., see Bersani, M. 203-204 (2003) 281
- Gnaser, H., Ionization probability of sputtered cluster anions: C_n^- and Si_n^- 203-204 (2003) 78
- Godines, A., see Villegas, A. 203-204 (2003) 94
- Gondran, C., see Bennett, J. 203-204 (2003) 409
- Gong, H., see Amemiya, T. 203-204 (2003) 738
- Gong, H., see Kinoshita, A. 203-204 (2003) 742
- Gong, H., T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi, Time-of-flight secondary ion mass spectrometry of fatty acids in rat retina 203-204 (2003) 734
- Gonze, X., see Delcorte, A. 203-204 (2003) 106
- Gonze, X., see Wojciechowski, I. 203-204 (2003) 102
- Goto, K., see Takano, A. 203-204 (2003) 294
- Granger, C.N., see Schueler, B.W. 203-204 (2003) 847
- Grehl, T., R. Möllers and E. Niehuis, Low energy dual beam depth profiling: influence of sputter and analysis beam parameters on profile performance using TOF-SIMS 203-204 (2003) 277
- Gross, Th., I. Retzko, J. Friedrich and W. Unger, Time-of-flight-SIMS and XPS characterization of metal doped polymers 203-204 (2003) 575
- Grossi, A., see Zanderigo, F. 203-204 (2003) 437
- Guillemot, L., see Staicu-Casagrande, E.M. 203-204 (2003) 86
- Güllich, H., see Maier, M. 203-204 (2003) 486
- Gunst, U., see Feldner, J.C. 203-204 (2003) 722
- Guzmán, B., J.J. Serrano, J.M. Blanco, M. Aguilar and O. Ameziane, Simulation of SiO_2 build-up in silicon under oxygen bombardment 203-204 (2003) 139
- Guzmán, B., see Dowsett, M.G. 203-204 (2003) 273
- Guzmán, B., see Dowsett, M.G. 203-204 (2003) 363
- Hagenhoff, B., see Kersting, R. 203-204 (2003) 561
- Hallett, K., D. Thickett, D.S. McPhail and R.J. Chater, Application of SIMS to silver tarnish at the British Museum 203-204 (2003) 789
- Han, S., see Lee, Y. 203-204 (2003) 875
- Haneda, H., A study of defect structures in oxide materials by secondary ion mass spectrometry 203-204 (2003) 625
- Haneda, H., see Park, D.-C. 203-204 (2003) 359
- Hasegawa, T., see Tomita, M. 203-204 (2003) 465
- Hashimoto, K., see Takeuchi, T. 203-204 (2003) 605
- Hashimoto, S., see Tomita, M. 203-204 (2003) 465
- Hayashi, S., and K. Yanagihara, Dual ion beam analysis of boron implanted SiO_2 /silicon interface 203-204 (2003) 339
- Hayashi, S., A. Takano, H. Takenaka and Y. Homma, SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams 203-204 (2003) 298
- Hayashi, S., see Saito, R. 203-204 (2003) 508
- Hayashi, S., see Takano, A. 203-204 (2003) 294
- Hayashi, S., see Tomita, M. 203-204 (2003) 465
- Hayashi, S., T. Sasaki, K. Kawamura, A. Matsumura, K. Yanagihara and K. Tanaka, SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation 203-204 (2003) 504
- Hayashi, Y., see Yamamoto, Y. 203-204 (2003) 863
- Haynie, B.C., A.V. Walker, T.B. Tighe, D.L. Allara and N. Winograd, Adventures in molecular electronics: how to attach wires to molecules 203-204 (2003) 433
- Hellsing, M., M. Fokine, Å. Claesson, L.-E. Nilsson and W. Margulis, ToF-SIMS imaging of dopant diffusion in optical fibers 203-204 (2003) 648
- Herres, N., see Maier, M. 203-204 (2003) 486
- Higashi, Y., see Homma, Y. 203-204 (2003) 35
- Higashi, Y., see Kanazawa, M. 203-204 (2003) 152
- Higashi, Y., see Takano, A. 203-204 (2003) 294
- Hill, R., see Davies, N. 203-204 (2003) 223
- Hill, R., see Gibbons, R. 203-204 (2003) 343
- Hill, R., see Wong, S.C.C. 203-204 (2003) 219
- Hillion, F., see Slodzian, G. 203-204 (2003) 798

- Hishita, S., see Park, D.-C. 203-204 (2003) 359
- Hitzman, C., see Hombourger, C. 203-204 (2003) 383
- Hockett, R.S., see Fujiyama, N. 203-204 (2003) 457
- Högberg, J., see Sjövall, P. 203-204 (2003) 669
- Holliger, P., see Laugier, F. 203-204 (2003) 348
- Hombourger, C., P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman, LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures 203-204 (2003) 383
- Homma, Y., A. Takano and Y. Higashi, Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model 203-204 (2003) 35
- Homma, Y., see Hayashi, S. 203-204 (2003) 298
- Homma, Y., see Kanazawa, M. 203-204 (2003) 152
- Homma, Y., see Takano, A. 203-204 (2003) 294
- Homma, Y., see Tomita, M. 203-204 (2003) 465
- Hong, T.E., see Cho, S.B. 203-204 (2003) 302
- Hong, T.E., see Shon, H.K. 203-204 (2003) 423
- Hongo, C., M. Tomita, M. Takenaka and A. Murakoshi, Accurate SIMS depth profiling for ultra-shallow implants using backside SIMS 203-204 (2003) 264
- Hopstaken, M.J.P., see van Berkum, J.G.M. 203-204 (2003) 414
- Horbett, T.A., see Wagner, M.S. 203-204 (2003) 704
- Horita, T., K. Yamaji, N. Sakai, Y. Xiong, T. Kato, H. Yokokawa and T. Kawada, Determination of proton and oxygen movements in solid oxides by the tracer gases exchange technique and secondary ion mass spectrometry 203-204 (2003) 634
- Horreard, F., see Slodzian, G. 203-204 (2003) 798
- Hoshi, T., and M. Kudo, High resolution static SIMS imaging by time of flight SIMS 203-204 (2003) 818
- Hoshi, T., see Li, Z. 203-204 (2003) 318
- Hoshi, T., see Li, Z. 203-204 (2003) 323
- Hoshi, T., see Takahara, A. 203-204 (2003) 538
- Hoshi, T., see Tomiyasu, B. 203-204 (2003) 775
- Hou, A., see Bennett, J. 203-204 (2003) 409
- Houssiau, L., and P. Bertrand, TOF-SIMS study of organosilane adsorption on model hydroxyl terminated surfaces 203-204 (2003) 580
- Hult, A., see Coullerez, G. 203-204 (2003) 620
- Hung, P.Y., see Bennett, J. 203-204 (2003) 409
- Huyghebaert, C., B. Brijs, T. Janssens and W. Vandervorst, Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe 203-204 (2003) 56
- Huyghebaert, C., see Janssens, T. 203-204 (2003) 30
- Huyghebaert, C., see Janssens, T. 203-204 (2003) 90
- Huyghebaert, C., T. Janssens, B. Brijs and W. Vandervorst, Ionization probability changes of the Si^+ ions during the transient for 3 keV O_2^+ bombardment of Si 203-204 (2003) 134
- Hwang, C.H., see Kang, H. 203-204 (2003) 842
- Hwang, J.F., see Chen, C.Y. 203-204 (2003) 461
- Hwang, M.C., see Chen, C.Y. 203-204 (2003) 461
- Iacob, E., see Lazzeri, P. 203-204 (2003) 445
- Iacob, E., see Lazzeri, P. 203-204 (2003) 767
- Imai, N., see Togashi, S. 203-204 (2003) 814
- Ino, T., see Shichi, H. 203-204 (2003) 228
- Inoue, M., see Takano, A. 203-204 (2003) 294
- Inoue, N., see Fujiyama, N. 203-204 (2003) 457
- Ishida, M., see Yamamura, Y. 203-204 (2003) 62
- Ishikawa, Y., see Shibahara, K. 203-204 (2003) 387
- Ishiwata, O., see Ueki, Y. 203-204 (2003) 453
- Itina, T.E., see Garrison, B.J. 203-204 (2003) 67
- Iwai, K., see Takeuchi, T. 203-204 (2003) 605
- Iwanejko, I., see Konarski, P. 203-204 (2003) 757
- Izawa, C., H.-H. Uchida, H. Okuhira and Y. Nishi, Hydrogen absorption of $LaNi_5$ after LiOD treatment and surface characterization by TOF-SIMS 203-204 (2003) 665
- Jacobson, D.C., see Magee, C.W. 203-204 (2003) 310
- Jagadish, C., see Linnarsson, M.K. 203-204 (2003) 427
- Jahnel, F., and R. von Criegern, Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for microelectronics support applications 203-204 (2003) 367
- Janson, M.S., see Linnarsson, M.K. 203-204 (2003) 427
- Janssen, R.A.J., see Bulle-Lieuwma, C.W.T. 203-204 (2003) 547
- Janssens, T., C. Huyghebaert and W. Vandervorst, Towards a model for the formation of positive Si^+ ions 203-204 (2003) 90
- Janssens, T., C. Huyghebaert, W. Vandervorst, A. Gildenpfennig and H.H. Brongersma, On the correlation between Si^+ yields and surface oxygen concentration using in situ SIMS-LEIS 203-204 (2003) 30
- Janssens, T., see Huyghebaert, C. 203-204 (2003) 56
- Janssens, T., see Huyghebaert, C. 203-204 (2003) 134
- Janssens, T., see Vandervorst, W. 203-204 (2003) 371
- Jomard, F., and D. Ballutaud, SIMS analysis of hydrogen diffusion and trapping in CVD polycrystalline diamond 203-204 (2003) 478
- Jonkheijm, P., see Bulle-Lieuwma, C.W.T. 203-204 (2003) 547
- Jungnickel, H., see Cliff, B. 203-204 (2003) 710
- Kajiyama, T., see Takahara, A. 203-204 (2003) 538
- Kakehashi, S., see Tomita, M. 203-204 (2003) 465
- Kakibayashi, H., see Shichi, H. 203-204 (2003) 228
- Kamischke, R., see Kollmer, F. 203-204 (2003) 238
- Kamoto, R., see Yamada, K. 203-204 (2003) 512
- Kanazawa, M., A. Takano, Y. Higashi, M. Suzuki and Y. Homma, Observation of ripple formation on O_2^+ -irradiated GaN surfaces using atomic force microscopy 203-204 (2003) 152
- Kanda, Y., see Nojima, M. 203-204 (2003) 194
- Kanehori, K., see Shichi, H. 203-204 (2003) 228
- Kang, H., C.W. Lee, C.H. Hwang and C.M. Kim, Probing molecules on a surface by Cs^+ reactive ion scattering: identification of C_2H_x ($x \leq 4$) hydrocarbons 203-204 (2003) 842

- Kang, H.J., see Cho, S.B. 203-204 (2003) 302
 Kang, H.J., see Shon, H.K. 203-204 (2003) 423
 Karashima, M., see Tanaka, Y. 203-204 (2003) 205
 Karen, A., N. Man, T. Shibamori and K. Takahashi, TOF-SIMS characterization of industrial materials: from silicon wafer to polymer 203-204 (2003) 541
 Karen, A., see Fujiyama, N. 203-204 (2003) 457
 Karen, A., see Shibamori, T. 203-204 (2003) 449
 Karen, A., see Yamada, K. 203-204 (2003) 512
 Karen, A., see Yamamoto, T. 203-204 (2003) 516
 Karim, A., see Roberson, S. 203-204 (2003) 855
 Kataoka, Y., K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack, Surface roughening of silicon under ultra-low-energy cesium bombardment 203-204 (2003) 43
 Kataoka, Y., M. Shigeno, Y. Tada and K. Wittmaack, Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams 203-204 (2003) 329
 Kato, T., see Horita, T. 203-204 (2003) 634
 Kawada, T., see Horita, T. 203-204 (2003) 634
 Kawaguchi, D., see Takahara, A. 203-204 (2003) 538
 Kawamura, K., see Hayashi, S. 203-204 (2003) 504
 Kawai, H., see Kuroki, H. 203-204 (2003) 867
 Kawashima, T., see Ueki, Y. 203-204 (2003) 453
 Kazama, Y., see Tomita, M. 203-204 (2003) 465
 Kazantsev, D.Yu., see Alexandrov, O.V. 203-204 (2003) 520
 Kazantsev, D.Yu., see Ya Ber, B. 203-204 (2003) 184
 Kelly, J., see Gibbons, R. 203-204 (2003) 343
 Kelly, J., see Rees, E.E. 203-204 (2003) 660
 Kelly, J.H., M.G. Dowsett, P. Augustus and R. Beanland, Correction for the loss of depth resolution with accurate depth calibration when profiling with Cs⁺ at angles of incidence above 50° to normal 203-204 (2003) 260
 Kelly, J.H., see Dowsett, M.G. 203-204 (2003) 273
 Kersting, R., B. Hagenhoff, P. Pijpers and R. Verlaek, The influence of primary ion bombardment conditions on the secondary ion emission behavior of polymer additives 203-204 (2003) 561
 Kheyrandish, H., see Dowsett, M.G. 203-204 (2003) 500
 Kikkawa, T., see Shibahara, K. 203-204 (2003) 387
 Kilo, M., see Weber, S. 203-204 (2003) 656
 Kim, C.M., see Kang, H. 203-204 (2003) 842
 Kim, H.K., see Cho, S.B. 203-204 (2003) 302
 Kim, H.K., see Shon, H.K. 203-204 (2003) 423
 Kim, J.-S., see Lee, Y. 203-204 (2003) 875
 Kim, K.J., see Cho, S.B. 203-204 (2003) 302
 Kim, K.J., see Shon, H.K. 203-204 (2003) 423
 Kim, Y.-S., see Lee, Y. 203-204 (2003) 875
 Kimura, K., K. Nakajima, H. Kobayashi, S. Miwa and K. Satori, SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films 203-204 (2003) 418
 King, B.V., M.J. Pellin, J.F. Moore, I.V. Veryovkin, M.R. Savina and C.E. Tripa, Estimation of useful yield in surface analysis using single photon ionisation 203-204 (2003) 244
 King, B.V., see Tan, M. 203-204 (2003) 248
 Kinoshita, A., H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi, Trace elements in lenses of normal Wistar Kyoto rats 203-204 (2003) 742
 Kirkwood, D., see Bellingham, J. 203-204 (2003) 851
 Kita, N.T., S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita, Application of high precision SIMS ²⁶Al-²⁶Mg analyses to the early solar system chronology 203-204 (2003) 806
 Kita, N.T., see Togashi, S. 203-204 (2003) 814
 Kobayashi, H., see Kimura, K. 203-204 (2003) 418
 Koezuka, K., see Tomita, M. 203-204 (2003) 465
 Köhler, K., see Maier, M. 203-204 (2003) 486
 Kollmer, F., N. Bourdos, R. Kamischke and A. Benninghoven, Nonresonant Laser-SNMS and TOF-SIMS analysis of sub-μm structures 203-204 (2003) 238
 Komatsu, M., see Abe, Y. 203-204 (2003) 859
 Konarski, P., and A. Mierzejewska, B₄C/Mo/Si and Ta₂O₅/Ta nanostructures analysed by ultra-low energy argon ion beams 203-204 (2003) 354
 Konarski, P., I. Iwanejko and A. Mierzejewska, SIMS depth profiling of working environment nanoparticles 203-204 (2003) 757
 Kovarsky, A.P., see Alexandrov, O.V. 203-204 (2003) 520
 Kovarsky, A.P., see Belykh, S.F. 203-204 (2003) 122
 Kovarsky, A.P., see Ya Ber, B. 203-204 (2003) 184
 Kozuka, S., see Tomita, M. 203-204 (2003) 377
 Krantzman, K.D., see Garrison, B.J. 203-204 (2003) 67
 Kriegeskotte, C., see Fartmann, M. 203-204 (2003) 726
 Krüger, D., A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova, Transient processes and structural transformations in Si₁Ge_{1-x} layers during oxygen implantation and sputtering 203-204 (2003) 285
 Kudo, M., see Hoshi, T. 203-204 (2003) 818
 Kudo, M., see Miyoshi, H. 203-204 (2003) 473
 Kudo, M., see Saito, R. 203-204 (2003) 508
 Kudo, M., see Yamamoto, Y. 203-204 (2003) 863
 Kudriavtsev, Yu., see Villegas, A. 203-204 (2003) 94
 Kunihiro, T., see Yurimoto, H. 203-204 (2003) 793
 Kuroki, H., and H. Kawai, Oxidizing mechanism of beryllium-copper in alkaline solution 203-204 (2003) 867
 Kuroki, H., see Tomita, M. 203-204 (2003) 465
 Kurps, R., see Krüger, D. 203-204 (2003) 285
 Kusama, K., see Tomita, M. 203-204 (2003) 465
 Kwon, M.-H., see Lee, Y. 203-204 (2003) 875
 Labarthe, A., see Audinot, J.-N. 203-204 (2003) 718
 Lacombe, S., see Staicu-Casagrande, E.M. 203-204 (2003) 86
 Laugier, F., P. Holliger, J.C. Dupuy and N. Baboux, Comparison between Xe⁺ and O₂⁺ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures 203-204 (2003) 348

- Lausmaa, J., see Sjövall, P. 203-204 (2003) 669
- Lazzeri, P., G. Clauser, E. Iacob, A. Lui, G. Tonidandel and M. Anderle, ToF-SIMS and XPS characterisation of urban aerosols for pollution studies 203-204 (2003) 767
- Lazzeri, P., G. Franco, M. Garozzo, C. Gerardi, E. Iacob, A. Lo Faro, A. Privitera, L. Vanzetti and M. Bersani, TOF-SIMS study of adhesive residuals on device contact pads after wafer taping and backgrinding 203-204 (2003) 445
- Lazzeri, P., see Bersani, M. 203-204 (2003) 281
- Ledermann, N., see Coullerez, G. 203-204 (2003) 527
- Lee, C.W., see Kang, H. 203-204 (2003) 842
- Lee, H.I., see Cho, S.B. 203-204 (2003) 302
- Lee, H.I., see Moon, D.W. 203-204 (2003) 27
- Lee, J.H., see Chen, C.Y. 203-204 (2003) 461
- Lee, Y., S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim, Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry 203-204 (2003) 875
- Lenaerts, J., R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens, Imaging TOF-SIMS for the surface analysis of silver halide microcrystals 203-204 (2003) 614
- Li, Z., see Tomita, M. 203-204 (2003) 465
- Li, Z., T. Hoshi and R. Oiwa, Six months repeatability of D-SIMS depth profile using an ultra-low-energy probe 203-204 (2003) 318
- Li, Z., T. Hoshi and R. Oiwa, Characteristics of ultra-low-energy Cs⁺ ion beam bombardments 203-204 (2003) 323
- Liangzhen, C., see Xin, G. 203-204 (2003) 441
- Licciardello, A., A. Auditore, F. Samperi and C. Puglisi, Surface evolution of polycarbonate/polyethylene terephthalate blends induced by thermal treatments 203-204 (2003) 556
- Licciardello, A., see Médard, N. 203-204 (2003) 571
- Liew, T., see Zhu, L. 203-204 (2003) 871
- Li-Fatou, A.V., and M. Douglas, Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation 203-204 (2003) 290
- Lim, H., see Lee, Y. 203-204 (2003) 875
- Lim, M.S., see van der Heide, P.A.W. 203-204 (2003) 156
- Lin, G.C., see Chen, C.Y. 203-204 (2003) 461
- Lindley, P., see Mowat, I. 203-204 (2003) 495
- Lindsay, R., see Vandervorst, W. 203-204 (2003) 371
- Lindstroem, G., see Barcz, A. 203-204 (2003) 396
- Ling, Y.C., see Chen, C.Y. 203-204 (2003) 461
- Ling, Y.C., see Chen, C.Y. 203-204 (2003) 779
- Ling, Y.C., see Chiou, C.Y. 203-204 (2003) 482
- Linnarsson, M.K., U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson, Solubility limits of dopants in 4H-SiC 203-204 (2003) 427
- Lipinsky, D., see Fartmann, M. 203-204 (2003) 726
- Lipinsky, D., see Feldner, J.C. 203-204 (2003) 722
- Liu, R., C.M. Ng and A.T.S. Wee, Surface roughening effect in sub-keV SIMS depth profiling 203-204 (2003) 256
- Liu, R., see Yeo, K.L. 203-204 (2003) 335
- Liu, Y.Z., see Kita, N.T. 203-204 (2003) 806
- Lo Faro, A., see Lazzeri, P. 203-204 (2003) 445
- Lockyer, N., see Davies, N. 203-204 (2003) 223
- Lockyer, N.P., see Cliff, B. 203-204 (2003) 710
- Lockyer, N.P., see Cliff, B. 203-204 (2003) 730
- Lockyer, N.P., see Wong, S.C.C. 203-204 (2003) 219
- Loibl, N., see Gibbons, R. 203-204 (2003) 343
- Loo, R., see Vandervorst, W. 203-204 (2003) 371
- Lörinčík, J., see Franzreb, K. 203-204 (2003) 39
- Lui, A., see Lazzeri, P. 203-204 (2003) 767
- Lundmark, S., see Coullerez, G. 203-204 (2003) 620
- Magee, C.W., and D.C. Jacobson, Using SIMS and the NIST standard reference material #2137 to calibrate standards used in the ¹¹B(p, α)⁸Be nuclear reaction analysis of B in Si 203-204 (2003) 310
- Magnusson, H., see Coullerez, G. 203-204 (2003) 620
- Maier, M., D. Serries, T. Geppert, K. Köhler, H. Güllich and N. Herres, SIMS depth profiling of InGaAsN/InAlAs quantum wells on InP 203-204 (2003) 486
- Makino, N., see Saito, R. 203-204 (2003) 508
- Maksimov, S.E., see Dzhemilev, N.Kh. 203-204 (2003) 118
- Malkoch, M., see Coullerez, G. 203-204 (2003) 620
- Malmström, E., see Coullerez, G. 203-204 (2003) 620
- Man, N., see Karen, A. 203-204 (2003) 541
- Man, N., see Shibamori, T. 203-204 (2003) 449
- Margulis, W., see Hellsing, M. 203-204 (2003) 648
- Mathieu, H.J., see Coullerez, G. 203-204 (2003) 527
- Mathieu, H.J., see Coullerez, G. 203-204 (2003) 620
- Matsumura, A., see Hayashi, S. 203-204 (2003) 504
- Matsunaga, T., see Yoshikawa, S. 203-204 (2003) 252
- Matsuo, J., see Toyoda, N. 203-204 (2003) 214
- Matsuoka, K., see Toujou, F. 203-204 (2003) 590
- Maul, J.L., see Dowsett, M.G. 203-204 (2003) 500
- McCaig, L., see Mowat, I. 203-204 (2003) 495
- McCaig, L., see Schueler, B.W. 203-204 (2003) 847
- McConville, C.F., see Dowsett, M.G. 203-204 (2003) 363
- McKinley, J.M., see Schueler, B.W. 203-204 (2003) 847
- McPhail, D.S., see Alibhai, A.A. 203-204 (2003) 630
- McPhail, D.S., see Hallett, K. 203-204 (2003) 789
- McPhail, D.S., see Rees, E.E. 203-204 (2003) 660
- McQuaw, C.M., see Garrison, B.J. 203-204 (2003) 67
- Médard, N., A. Benninghoven, D. Rading, A. Licciardello, A. Auditore, T.M. Duc, H. Montigaud, F. Vernerey, C. Poleunis and P. Bertrand, Antioxidant segregation and crystallisation at polyester surfaces studied by ToF-SIMS 203-204 (2003) 571
- Medvedeva, M., I. Wojciechowski and B.J. Garrison, Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface 203-204 (2003) 148
- Metz, J., see Schueler, B.W. 203-204 (2003) 847

- Meyer, S., C. Staudt and A. Wucher, Ionization probability of atoms and molecules sputtered from a cesium covered silver surface 203-204 (2003) 48
- Mierzejewska, A., see Konarski, P. 203-204 (2003) 354
- Mierzejewska, A., see Konarski, P. 203-204 (2003) 757
- Migeon, H.-N., see Audinot, J.-N. 203-204 (2003) 718
- Migeon, H.-N., see Ruch, D. 203-204 (2003) 566
- Migeon, H.-N., see Wirtz, T. 203-204 (2003) 189
- Miki, T., see Nishi, A. 203-204 (2003) 470
- Mitsui, Y., see Shichi, H. 203-204 (2003) 228
- Miwa, S., see Kimura, K. 203-204 (2003) 418
- Miwa, S., see Tomita, M. 203-204 (2003) 465
- Miyaki, S., A. Yoshida, Y. Yamamoto and K. Takeuchi, Failure analysis of liquid crystal display panel by time-of-flight secondary ion mass spectrometry 203-204 (2003) 836
- Miyaki, S., see Tomita, M. 203-204 (2003) 465
- Miyamoto, I., see Takeuchi, T. 203-204 (2003) 605
- Miyoshi, H., R. Saito and M. Kudo, Surface chemical state analysis of electroplated Cu film under Cu-CMP process by means of TOF-SIMS 203-204 (2003) 473
- Möllers, R., see Grehl, T. 203-204 (2003) 277
- Momiji, K., see Takeuchi, T. 203-204 (2003) 605
- Monsallut, P., see De Chambost, E. 203-204 (2003) 391
- Montigaud, H., see Médard, N. 203-204 (2003) 571
- Moon, D.W., and H.I. Lee, The dose dependence of Si sputtering with low energy ions in shallow depth profiling 203-204 (2003) 27
- Moon, D.W., see Cho, S.B. 203-204 (2003) 302
- Moon, D.W., see Shon, H.K. 203-204 (2003) 423
- Moore, J.F., see King, B.V. 203-204 (2003) 244
- Morishita, Y., and H. Satoh, Silicon isotope fractionation during FZ growth of silicon crystals 203-204 (2003) 802
- Morishita, Y., see Kita, N.T. 203-204 (2003) 806
- Morishita, Y., see Togashi, S. 203-204 (2003) 814
- Morita, H., see Tsukamoto, K. 203-204 (2003) 404
- Morita, H., see Yoshikawa, S. 203-204 (2003) 252
- Morita, N., see Yamamoto, T. 203-204 (2003) 516
- Morris, R., see Dowsett, M.G. 203-204 (2003) 500
- Mostefaoui, S., see Kita, N.T. 203-204 (2003) 806
- Mowat, I., P. Lindley and L. McCaig, A correlation of TOF-SIMS and TXRF for the analysis of trace metal contamination on silicon and gallium arsenide 203-204 (2003) 495
- Mowat, I., see Schueler, B.W. 203-204 (2003) 847
- Muller, J.F., see Ruch, D. 203-204 (2003) 566
- Muraji, Y., see Shibamori, T. 203-204 (2003) 449
- Murakoshi, A., see Hongo, C. 203-204 (2003) 264
- Murakoshi, A., see Tomita, M. 203-204 (2003) 377
- Mural, P., see Coullerez, G. 203-204 (2003) 527
- Muramoto, T., and Y. Yamamura, MD simulation of cluster ejection due to sputtering by polyatomic projectiles 203-204 (2003) 143
- Murase, A., and T. Ohmori, TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material 203-204 (2003) 586
- Murota, J., see Krüger, D. 203-204 (2003) 285
- Nagashima, K., see Yurimoto, H. 203-204 (2003) 793
- Nagatomo, M., see Saito, R. 203-204 (2003) 508
- Nakajima, K., see Kimura, K. 203-204 (2003) 418
- Ng, C.M., see Liu, R. 203-204 (2003) 256
- Ng, C.M., see Yeo, K.L. 203-204 (2003) 335
- Niehuys, E., see Grehl, T. 203-204 (2003) 277
- Niemantsverdriet, J.W., see Bulle-Lieuwma, C.W.T. 203-204 (2003) 547
- Nihei, Y., Preface 203-204 (2003) 3
- Nihei, Y., see Nojima, M. 203-204 (2003) 194
- Nihei, Y., see Sakamoto, T. 203-204 (2003) 762
- Nihei, Y., see Takanashi, K. 203-204 (2003) 609
- Nihei, Y., see Tanaka, Y. 203-204 (2003) 205
- Nihei, Y., see Tomiyasu, B. 203-204 (2003) 775
- Nilsson, L.-E., see Hellsing, M. 203-204 (2003) 648
- Nishi, A., M. Sado, T. Miki and Y. Fukui, Evaluation of the Cu-CMP process by TOF-SIMS and XPS: time dependence of Cu surface adsorbents and oxidation states 203-204 (2003) 470
- Nishi, Y., see Izawa, C. 203-204 (2003) 665
- Noakes, T.C.Q., see Dowsett, M.G. 203-204 (2003) 363
- Nohira, H., see Conard, T. 203-204 (2003) 400
- Nojima, M., B. Tomiyasu, Y. Kanda, M. Owari and Y. Nihei, Nanoscale SIMS analysis: the next generation in local analysis 203-204 (2003) 194
- Nossarzewska, E., see Barcz, A. 203-204 (2003) 396
- Oda, T., see Shibahara, K. 203-204 (2003) 387
- Ohashi, N., see Park, D.-C. 203-204 (2003) 359
- Ohashi, Y., see Amemiya, T. 203-204 (2003) 738
- Ohashi, Y., see Gong, H. 203-204 (2003) 734
- Ohashi, Y., see Kinoshita, A. 203-204 (2003) 742
- Ohmori, T., see Murase, A. 203-204 (2003) 586
- Ohya, K., Dynamic behavior of sputtering of implanted projectiles and target atoms under high fluence gallium ion bombardment 203-204 (2003) 82
- Oishi, S., M. Shirahase, M. Sado and R. Oiwa, Analysis of condensation dusts from the heavy oil combustion using TOF-SIMS 203-204 (2003) 772
- Oiwa, R., see Li, Z. 203-204 (2003) 318
- Oiwa, R., see Li, Z. 203-204 (2003) 323
- Oiwa, R., see Oishi, S. 203-204 (2003) 772
- Okabe, M., see Takaya, K. 203-204 (2003) 684
- Okabe, M., T. Yoshida, R. Yoshii, M. Sawataishi and K. Takaya, Zinc detection in the islet of Langerhans by SIMS 203-204 (2003) 714
- Okamoto, Y., see Tomita, M. 203-204 (2003) 465
- Okuhira, H., see Abe, Y. 203-204 (2003) 175
- Okuhira, H., see Abe, Y. 203-204 (2003) 859
- Okuhira, H., see Izawa, C. 203-204 (2003) 665
- Okuno, K., see Tomita, M. 203-204 (2003) 465
- Okuno, K., see Yamamoto, T. 203-204 (2003) 516
- Olsson, M., see Bexell, U. 203-204 (2003) 596
- Onimatsu, D., see Shibahara, K. 203-204 (2003) 387

- Ono, N., see Takanashi, K. 203-204 (2003) 609
- Ormsby, T.J., see Dowsett, M.G. 203-204 (2003) 273
- Ormsby, T.J., see Dowsett, M.G. 203-204 (2003) 363
- Osabe, S., see Shichi, H. 203-204 (2003) 228
- Osakabe, K., see Tadokoro, N. 203-204 (2003) 72
- Ostrop, M., see Arlinghaus, H.F. 203-204 (2003) 689
- Ostrop, M., see Feldner, J.C. 203-204 (2003) 722
- Owari, M., see Nojima, M. 203-204 (2003) 194
- Owari, M., see Sakamoto, T. 203-204 (2003) 762
- Owari, M., see Takanashi, K. 203-204 (2003) 609
- Owari, M., see Tanaka, Y. 203-204 (2003) 205
- Owari, M., see Tomiyasu, B. 203-204 (2003) 775
- Palitsin, V.V., see Belykh, S.F. 203-204 (2003) 122
- Palitsin, V.V., see Belykh, S.F. 203-204 (2003) 126
- Park, D.-C., I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda, SIMS depth profiling of N and In in a ZnO single crystal 203-204 (2003) 359
- Pasquet, B., see Rasser, B. 203-204 (2003) 673
- Patel, S.B., see Dowsett, M.G. 203-204 (2003) 500
- Pellin, M.J., see King, B.V. 203-204 (2003) 244
- Perego, M., S. Ferrari, S. Spiga and M. Fanciulli, Nanocrystals depth profiling by means of Cs⁺ in negative polarity with dual beam ToF-SIMS 203-204 (2003) 110
- Perego, M., see Ferrari, S. 203-204 (2003) 52
- Perry, S.S., see van der Heide, P.A.W. 203-204 (2003) 156
- Peterson, R.E., and B.J. Tyler, Surface composition of atmospheric aerosol: individual particle characterization by TOF-SIMS 203-204 (2003) 751
- Petry, J., see Conard, T. 203-204 (2003) 400
- Peytier, I., see Vandervorst, W. 203-204 (2003) 371
- Pijpers, P., see Kersting, R. 203-204 (2003) 561
- Poleunis, C., C. Rubio, C. Compère and P. Bertrand, ToF-SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions 203-204 (2003) 693
- Poleunis, C., see Aubriet, F. 203-204 (2003) 114
- Poleunis, C., see Aubriet, F. 203-204 (2003) 180
- Poleunis, C., see Médard, N. 203-204 (2003) 571
- Pregnotato, A., see Zanderigo, F. 203-204 (2003) 437
- Prince, K., see Gard, F.S. 203-204 (2003) 490
- Privitera, A., see Lazzeri, P. 203-204 (2003) 445
- Puglisi, C., see Licciardello, A. 203-204 (2003) 556
- Queirolo, G., see Zanderigo, F. 203-204 (2003) 437
- Rading, D., see Médard, N. 203-204 (2003) 571
- Rasser, B., L. Desgranges and B. Pasquet, A new shielded SIMS instrument for analysis of highly radioactive materials 203-204 (2003) 673
- Rasser, B., see De Chambost, E. 203-204 (2003) 391
- Rees, E.E., D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett, Low energy SIMS characterisation of ultra thin oxides on ferrous alloys 203-204 (2003) 660
- Reich, D.F., see Schueler, B.W. 203-204 (2003) 847
- Retzko, I., see Gross, Th. 203-204 (2003) 575
- Richard, O., see Conard, T. 203-204 (2003) 400
- Richards, D., see Gibbons, R. 203-204 (2003) 343
- Riley, J.D., see Gard, F.S. 203-204 (2003) 490
- Roberson, S., A. Sehgal, A. Fahey and A. Karim, Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of bio-surfaces 203-204 (2003) 855
- Rocca, S., see Zanderigo, F. 203-204 (2003) 437
- Romanova, G.Ph., see Krüger, D. 203-204 (2003) 285
- Rowlands, G., see Dowsett, M.G. 203-204 (2003) 273
- Rubio, C., see Poleunis, C. 203-204 (2003) 693
- Ruch, D., C. Boes, R. Zimmer, J.F. Muller and H.-N. Migeon, Quantitative analysis of styrene butadiene copolymers using S-SIMS and LA-FTICRMS 203-204 (2003) 566
- Ruch, D., see Audinot, J.-N. 203-204 (2003) 718
- Ryan, M.P., see Rees, E.E. 203-204 (2003) 660
- Sado, M., see Nishi, A. 203-204 (2003) 470
- Sado, M., see Oishi, S. 203-204 (2003) 772
- Saiki, K., see Takeuchi, T. 203-204 (2003) 605
- Saito, R., M. Nagatomo, N. Makino, S. Hayashi and M. Kudo, Characterization of ion-induced sodium migration in various kinds of silicon oxide films 203-204 (2003) 508
- Saito, R., see Miyoshi, H. 203-204 (2003) 473
- Saito, S., see Tomita, M. 203-204 (2003) 465
- Saitoh, W., see Seki, S. 203-204 (2003) 832
- Sakaguchi, I., Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition 203-204 (2003) 652
- Sakaguchi, I., see Park, D.-C. 203-204 (2003) 359
- Sakai, N., see Horita, T. 203-204 (2003) 634
- Sakamoto, T., K. Shibata, K. Takanashi, M. Owari and Y. Nihei, Analysis of surface composition and internal structure of fly ash particles using an ion and electron multibeam microanalyzer 203-204 (2003) 762
- Sakamoto, T., see Takanashi, K. 203-204 (2003) 609
- Sakamoto, T., see Tanaka, Y. 203-204 (2003) 205
- Sameshima, J., see Yamada, K. 203-204 (2003) 512
- Samperi, F., see Licciardello, A. 203-204 (2003) 556
- Sams, D.B., see Fujiyama, N. 203-204 (2003) 457
- Sano, Y., see Terada, K. 203-204 (2003) 810
- Sasaki, S., see Tomita, M. 203-204 (2003) 465
- Sasaki, T., see Hayashi, S. 203-204 (2003) 504
- Satoh, H., see Morishita, Y. 203-204 (2003) 802
- Satori, K., see Kimura, K. 203-204 (2003) 418
- Sauerwein, W., see Fartmann, M. 203-204 (2003) 726
- Savina, M.R., see King, B.V. 203-204 (2003) 244
- Sawataishi, M., see Takaya, K. 203-204 (2003) 684
- Sawataishi, M., see Okabe, M. 203-204 (2003) 714
- Scherrer, H., see Weber, S. 203-204 (2003) 656
- Scherrer, H., see Wirtz, T. 203-204 (2003) 189
- Scherrer, S., see Weber, S. 203-204 (2003) 656
- Schmücker, M., see Fielitz, P. 203-204 (2003) 639
- Schneider, H., see Fielitz, P. 203-204 (2003) 639

- Schöner, A., see Linnarsson, M.K. 203-204 (2003) 427
- Schueler, B.W., C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang, Surface metal standards produced by ion implantation through a removable layer 203-204 (2003) 847
- Schuhmacher, M., see De Chambost, E. 203-204 (2003) 391
- Schuhmacher, M., see Hombourger, C. 203-204 (2003) 383
- Seah, M.P., see Gilmore, I.S. 203-204 (2003) 551
- Seah, M.P., see Gilmore, I.S. 203-204 (2003) 600
- See, A., see Yeo, K.L. 203-204 (2003) 335
- Sehgal, A., see Roberson, S. 203-204 (2003) 855
- Seki, S., H. Tamura and W. Saitoh, Ion image enhancement using in-situ implantation of Cs^+ and O_2^+ ions 203-204 (2003) 832
- Serrano, J.J., see Guzmán, B. 203-204 (2003) 139
- Serries, D., see Maier, M. 203-204 (2003) 486
- Setter, N., see Coullerez, G. 203-204 (2003) 527
- Seyama, H., Application of SIMS to the analysis of environmental samples 203-204 (2003) 745
- Shen, M., see Wagner, M.S. 203-204 (2003) 704
- Shibahara, K., D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa, Copper drift in low dielectric constant insulator films caused by O_2^+ primary ion beam 203-204 (2003) 387
- Shibamori, T., see Karen, A. 203-204 (2003) 541
- Shibamori, T., Y. Muraji, N. Man and A. Karen, TOF-SIMS measurement of ultra-thin SiO_2 films prepared by the graded-etching method 203-204 (2003) 449
- Shibata, K., see Sakamoto, T. 203-204 (2003) 762
- Shichi, H., S. Osabe, M. Sugaya, T. Ino, H. Kakibayashi, K. Kanehori and Y. Mitsui, A resonance photoionization sputtered neutral mass spectrometry instrument for submicron microarea analysis of ULSI devices 203-204 (2003) 228
- Shichi, H., see Tomita, M. 203-204 (2003) 465
- Shigeno, M., see Kataoka, Y. 203-204 (2003) 43
- Shigeno, M., see Kataoka, Y. 203-204 (2003) 329
- Shimizu, R., see Takano, A. 203-204 (2003) 294
- Shimodaira, N., see Yamamoto, Y. 203-204 (2003) 863
- Shingu, K., see Fujiyama, N. 203-204 (2003) 457
- Shinohara, H., see Tomita, M. 203-204 (2003) 465
- Shirahase, M., see Oishi, S. 203-204 (2003) 772
- Shollock, B.A., see Alibhai, A.A. 203-204 (2003) 630
- Shon, H.K., H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon, Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS 203-204 (2003) 423
- Shon, H.K., see Cho, S.B. 203-204 (2003) 302
- Simakin, S.G., and V.K. Smirnov, The features of using of BO_2^- secondary ions for SIMS depth profiling of shallow boron implantation in silicon 203-204 (2003) 314
- Sjövall, P., J. Lausmaa, C. Tullin and J. Högberg, Chemical characterization of combustion deposits by TOF-SIMS 203-204 (2003) 669
- Slodzian, G., F. Hillion, F.J. Stadermann and F. Horreard, Oxygen isotopic measurements on the Cameca Nano-sims 50 203-204 (2003) 798
- Smiley, E.J., see Garrison, B.J. 203-204 (2003) 67
- Smirnov, V.K., see Simakin, S.G. 203-204 (2003) 314
- Smith, S., see Schueler, B.W. 203-204 (2003) 847
- Snijders, J.H.M., see van Berkum, J.G.M. 203-204 (2003) 414
- Sodhi, R.N., see Dimov, S.S. 203-204 (2003) 644
- Sohn, S., see Feldner, J.C. 203-204 (2003) 722
- Sparks, C., see Bennett, J. 203-204 (2003) 409
- Spiga, S., see Perego, M. 203-204 (2003) 110
- Šroubek, Z., see Franzreb, K. 203-204 (2003) 39
- Stadermann, F.J., see Slodzian, G. 203-204 (2003) 798
- Staicu-Casagrande, E.M., L. Guillemot, S. Lacombe and V.A. Esaulov, Electron transfer in ion interactions with chlorine covered silver surfaces 203-204 (2003) 86
- Staub, P.F., see Hombourger, C. 203-204 (2003) 383
- Staudt, C., see Meyer, S. 203-204 (2003) 48
- Stephens, G., see Cliff, B. 203-204 (2003) 710
- Stevie, F.A., see Schueler, B.W. 203-204 (2003) 847
- Sugaya, M., see Shichi, H. 203-204 (2003) 228
- Sugiyama, N., see Yamamoto, T. 203-204 (2003) 516
- Suzuki, M., see Kanazawa, M. 203-204 (2003) 152
- Suzuki, M., see Tomita, M. 203-204 (2003) 377
- Svensson, B.G., see Linnarsson, M.K. 203-204 (2003) 427
- Szymczak, W., and K. Wittmaack, Ion-to-neutral conversion in time-of-flight secondary ion mass spectrometry 203-204 (2003) 170
- Tachibana, Y., see Yamamoto, Y. 203-204 (2003) 863
- Tachibe, T., see Tomita, M. 203-204 (2003) 377
- Tada, Y., see Kataoka, Y. 203-204 (2003) 43
- Tada, Y., see Kataoka, Y. 203-204 (2003) 329
- Tadokoro, N., M. Yuki and K. Osakabe, Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry 203-204 (2003) 72
- Takahara, A., D. Kawaguchi, K. Tanaka, M. Tozu, T. Hoshi and T. Kajiyama, Analysis of surface composition of isotopic polymer blend based on time-of-flight secondary ion mass spectroscopy 203-204 (2003) 538
- Takahashi, K., see Karen, A. 203-204 (2003) 541
- Takanashi, K., M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei, Elemental distribution analysis of positive electrode material for a nickel metal hydride battery 203-204 (2003) 609
- Takanashi, K., see Sakamoto, T. 203-204 (2003) 762
- Takanashi, K., see Tanaka, Y. 203-204 (2003) 205
- Takano, A., see Hayashi, S. 203-204 (2003) 298
- Takano, A., see Homma, Y. 203-204 (2003) 35
- Takano, A., see Kanazawa, M. 203-204 (2003) 152
- Takano, A., Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu, Evaluation of SIMS depth resolution using

- delta-doped multilayers and mixing-roughness-information depth model 203-204 (2003) 294
- Takashima, H., see Takaya, K. 203-204 (2003) 684
- Takaya, K., M. Okabe, M. Sawataishi, H. Takashima and T. Yoshida, Fine structures and ion images on fresh frozen dried ultrathin sections by transmission electron and scanning ion microscopy 203-204 (2003) 684
- Takaya, K., see Amemiya, T. 203-204 (2003) 738
- Takaya, K., see Gong, H. 203-204 (2003) 734
- Takaya, K., see Kinoshita, A. 203-204 (2003) 742
- Takaya, K., see Okabe, M. 203-204 (2003) 714
- Takenaka, H., see Hayashi, S. 203-204 (2003) 298
- Takenaka, H., see Takano, A. 203-204 (2003) 294
- Takenaka, M., see Hongo, C. 203-204 (2003) 264
- Takeuchi, K., see Miyaki, S. 203-204 (2003) 836
- Takeuchi, T., K. Iwai, K. Momoji, I. Miyamoto, K. Saiki and K. Hashimoto, Characterization of methyl methacrylate oligomers using secondary ion mass spectrometry, APCI mass spectrometry and molecular orbital theory 203-204 (2003) 605
- Tamminga, Y., see van Berkum, J.G.M. 203-204 (2003) 414
- Tamura, H., see Seki, S. 203-204 (2003) 832
- Tan, M., and B.V. King, Energy distributions and excitation probability of nickel atoms sputtered from Ni₃Al, NiAl and Ni 203-204 (2003) 248
- Tanaka, K., see Hayashi, S. 203-204 (2003) 504
- Tanaka, K., see Takahara, A. 203-204 (2003) 538
- Tanaka, Y., M. Karashima, K. Takanashi, T. Sakamoto, M. Owari and Y. Nihei, Development of a chemically assisted micro-beam etching system for three-dimensional microanalysis 203-204 (2003) 205
- Tanaka, Y., see Takanashi, K. 203-204 (2003) 609
- Taylor, M.A., see Weber, S. 203-204 (2003) 656
- Terada, K., and Y. Sano, In situ U-Pb dating and REE analyses of phosphates in extraterrestrial materials 203-204 (2003) 810
- Thickett, D., see Hallett, K. 203-204 (2003) 789
- Tighe, T.B., see Haynie, B.C. 203-204 (2003) 433
- Tillack, B., see Krüger, D. 203-204 (2003) 285
- Togashi, S., N.T. Kita, A. Tomiya, Y. Morishita and N. Imai, Melt contribution to partitioning of trace element between plagioclase and basaltic magma of Fuji volcano, Japan 203-204 (2003) 814
- Togashi, S., see Kita, N.T. 203-204 (2003) 806
- Tomita, M., M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi, Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis 203-204 (2003) 377
- Tomita, M., see Hongo, C. 203-204 (2003) 264
- Tomita, M., T. Hasegawa, S. Hashimoto, S. Hayashi, Y. Homma, S. Kakehashi, Y. Kazama, K. Koezuka, H. Kuroki, K. Kusama, Z. Li, S. Miwa, S. Miyaki, Y. Okamoto, K. Okuno, S. Saito, S. Sasaki, H. Shichi, H. Shinohara, F. Toujou, Y. Ueki and Y. Yamamoto, SIMS round-robin study of depth profiling of arsenic implants in silicon 203-204 (2003) 465
- Tomiya, A., see Togashi, S. 203-204 (2003) 814
- Tomiyasu, B., see Nojima, M. 203-204 (2003) 194
- Tomiyasu, B., T. Hoshi, M. Owari and Y. Nihei, TOF-SIMS measurements for toxic air pollutants adsorbed on the surface of airborne particles 203-204 (2003) 775
- Tonidandel, G., see Lazzeri, P. 203-204 (2003) 767
- Toujou, F., K. Tsukamoto and K. Matsuoka, Characterization of lubricants for fluid dynamic bearing by TOF-SIMS 203-204 (2003) 590
- Toujou, F., see Tomita, M. 203-204 (2003) 465
- Toujou, F., see Tsukamoto, K. 203-204 (2003) 404
- Toujou, F., see Yoshikawa, S. 203-204 (2003) 252
- Toyoda, N., J. Matsuo, T. Aoki, I. Yamada and D.B. Fenner, Secondary ion mass spectrometry with gas cluster ion beams 203-204 (2003) 214
- Tozu, M., see Amemiya, T. 203-204 (2003) 738
- Tozu, M., see Gong, H. 203-204 (2003) 734
- Tozu, M., see Kinoshita, A. 203-204 (2003) 742
- Tozu, M., see Takahara, A. 203-204 (2003) 538
- Tripa, C.E., see King, B.V. 203-204 (2003) 244
- Tsukamoto, K., S. Yoshikawa, F. Toujou and H. Morita, Application of SIMS in microelectronics 203-204 (2003) 404
- Tsukamoto, K., see Toujou, F. 203-204 (2003) 590
- Tsukamoto, K., see Yoshikawa, S. 203-204 (2003) 252
- Tugushev, V.I., see Dzhemilev, N.Kh. 203-204 (2003) 118
- Tullin, C., see Sjövall, P. 203-204 (2003) 669
- Tyler, B., Interpretation of TOF-SIMS images: multivariate and univariate approaches to image de-noising, image segmentation and compound identification 203-204 (2003) 825
- Tyler, B.J., see Peterson, R.E. 203-204 (2003) 751
- Uchida, H.-H., see Izawa, C. 203-204 (2003) 665
- Ueki, Y., see Tomita, M. 203-204 (2003) 465
- Ueki, Y., T. Kawashima and O. Ishiwata, SIMS analysis of insulating multilayer including silicon nitride 203-204 (2003) 453
- Unger, W., see Gross, Th. 203-204 (2003) 575
- van Berkum, J.G.M., M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes, Quantitative depth profiling of SiO_xN_y layers on Si 203-204 (2003) 414
- van der Heide, P.A.W., and J. Bennett, Transient effects noted during Cs⁺ depth profile analysis of Si at high incidence angles 203-204 (2003) 306
- van der Heide, P.A.W., M.S. Lim, S.S. Perry and J. Bennett, Transient effects induced through ripple topography growth during Cs⁺ depth profile analysis of Si at high incidence angles 203-204 (2003) 156
- van Duren, J.K.J., see Bulle-Lieuwma, C.W.T. 203-204 (2003) 547

- van Gennip, W.J.H., see Bulle-Lieuwma, C.W.T. 203-204 (2003) 547
- Van Vaecck, L., see Lenaerts, J. 203-204 (2003) 614
- Vandervorst, W., see Conard, T. 203-204 (2003) 400
- Vandervorst, W., see De Witte, H. 203-204 (2003) 523
- Vandervorst, W., see Huyghebaert, C. 203-204 (2003) 56
- Vandervorst, W., see Huyghebaert, C. 203-204 (2003) 134
- Vandervorst, W., see Janssens, T. 203-204 (2003) 30
- Vandervorst, W., see Janssens, T. 203-204 (2003) 90
- Vandervorst, W., T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Fröhlich, A. Bergmaier and G. Dollinger, An (un)solvable problem in SIMS: B-interfacial profiling 203-204 (2003) 371
- Vanzetti, L., see Bersani, M. 203-204 (2003) 281
- Vanzetti, L., see Lazzeri, P. 203-204 (2003) 445
- Vering, G., C. Crone, J. Bijma and H.F. Arlinghaus, TOF-SIMS characterization of planktonic foraminifera 203-204 (2003) 785
- Verlaek, R., see Kersting, R. 203-204 (2003) 561
- Verlinden, G., see Lenaerts, J. 203-204 (2003) 614
- Vernerey, F., see Médard, N. 203-204 (2003) 571
- Veryovkin, I.V., see King, B.V. 203-204 (2003) 244
- Vickerman, J.C., see Cliff, B. 203-204 (2003) 710
- Vickerman, J.C., see Cliff, B. 203-204 (2003) 730
- Vickerman, J.C., see Davies, N. 203-204 (2003) 223
- Vickerman, J.C., see Wong, S.C.C. 203-204 (2003) 219
- Villegas, A., Yu. Kudriavtsev, A. Godines and R. Asomoza, Work function change caused by alkali ion sputtering 203-204 (2003) 94
- Viorner, C., see Coullerez, G. 203-204 (2003) 527
- von Criegern, R., see Jahnel, F. 203-204 (2003) 367
- Wagner, M.S., and D.G. Castner, Characterization of adsorbed protein films using time-of-flight-secondary ion mass spectrometry and multivariate analysis 203-204 (2003) 698
- Wagner, M.S., M. Shen, T.A. Horbett and D.G. Castner, Quantitative time-of-flight secondary ion mass spectrometry for the characterization of multicomponent adsorbed protein films 203-204 (2003) 704
- Walker, A.V., and N. Winograd, Prospects for imaging with TOF-SIMS using gold liquid metal ion sources 203-204 (2003) 198
- Walker, A.V., see Haynie, B.C. 203-204 (2003) 433
- Wang, C.C., see Chiou, C.Y. 203-204 (2003) 482
- Wang, J.T., see Chen, C.Y. 203-204 (2003) 779
- Weber, S., S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt, SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias 203-204 (2003) 656
- Wee, A.T.S., see Liu, R. 203-204 (2003) 256
- Wee, A.T.S., see Yeo, K.L. 203-204 (2003) 335
- Weibel, D.E., see Cliff, B. 203-204 (2003) 710
- Weibel, D.E., see Davies, N. 203-204 (2003) 223
- Weibel, D.E., see Wong, S.C.C. 203-204 (2003) 219
- Wen, M.L., see Chen, C.Y. 203-204 (2003) 461
- Weng, L.T., and C.-M. Chan, ToF-SIMS quantitative approaches in copolymers and polymer blends 203-204 (2003) 532
- Wennig, R., see Audinot, J.-N. 203-204 (2003) 718
- Wiesmann, H.P., see Fartmann, M. 203-204 (2003) 726
- Williams, P., see Franzreb, K. 203-204 (2003) 39
- Williams, P., see Franzreb, K. 203-204 (2003) 98
- Willich, P., see Fielitz, P. 203-204 (2003) 639
- Winograd, N., Prospects for imaging TOF-SIMS: from fundamentals to biotechnology 203-204 (2003) 13
- Winograd, N., see Garrison, B.J. 203-204 (2003) 67
- Winograd, N., see Haynie, B.C. 203-204 (2003) 433
- Winograd, N., see Walker, A.V. 203-204 (2003) 198
- Winograd, N., see Xu, J.Y. 203-204 (2003) 201
- Wirtz, T., H.-N. Migeon and H. Scherrer, Cation Mass Spectrometer: towards an optimisation of MCs^+ cluster analysis 203-204 (2003) 189
- Wittig, A., see Fartmann, M. 203-204 (2003) 726
- Wittmaack, K., Apparent and real transient effects in SIMS depth profiling using oxygen bombardment 203-204 (2003) 20
- Wittmaack, K., Detailed evaluation of the analytical resolution function 203-204 (2003) 268
- Wittmaack, K., see Kataoka, Y. 203-204 (2003) 43
- Wittmaack, K., see Kataoka, Y. 203-204 (2003) 329
- Wittmaack, K., see Szymczak, W. 203-204 (2003) 170
- Wojciechowski, I., A. Delcorte, X. Gonze and P. Bertrand, Mechanism of metal cationization in organic SIMS 203-204 (2003) 102
- Wojciechowski, I., see Delcorte, A. 203-204 (2003) 106
- Wojciechowski, I., see Medvedeva, M. 203-204 (2003) 148
- Wong, S.C.C., R. Hill, P. Blenkinsopp, N.P. Lockyer, D.E. Weibel and J.C. Vickerman, Development of a C_{60}^+ ion gun for static SIMS and chemical imaging 203-204 (2003) 219
- Wong-Leung, J., see Linnarsson, M.K. 203-204 (2003) 427
- Wucher, A., see Meyer, S. 203-204 (2003) 48
- Xanthopoulos, N., see Coullerez, G. 203-204 (2003) 527
- Xin, G., G. Dong, C. Xu, C. Liangzhen, O. Brox and A. Benninghoven, TOF-SIMS depth profiling of SIMON 203-204 (2003) 441
- Xiong, Y., see Horita, T. 203-204 (2003) 634
- Xu, C., see Xin, G. 203-204 (2003) 441
- Xu, J.Y., R.M. Braun and N. Winograd, Rapid screening of molecular arrays using imaging TOF-SIMS 203-204 (2003) 201
- Ya Ber, B., D.Yu. Kazantsev, A.P. Kovarsky and R.R. Yafaev, Determination of nitrogen in silicon carbide by secondary ion mass spectrometry 203-204 (2003) 184
- Yafaev, R.R., see Ya Ber, B. 203-204 (2003) 184
- Yamada, I., see Toyoda, N. 203-204 (2003) 214
- Yamada, K., N. Fujiyama, J. Sameshima, R. Kamoto and A. Karen, SIMS depth profile of copper in low- k dielectrics under electron irradiation for charge compensation 203-204 (2003) 512

- | | | | |
|---|--------------------|--|--------------------|
| Yamaji, K., see Horita, T. | 203-204 (2003) 634 | Yoshida, T., see Okabe, M. | 203-204 (2003) 714 |
| Yamamoto, T., N. Morita, N. Sugiyama, A. Karen and K. Okuno, Characterization of high- <i>k</i> gate dielectric films using SIMS | 203-204 (2003) 516 | Yoshida, T., see Takaya, K. | 203-204 (2003) 684 |
| Yamamoto, Y., see Miyaki, S. | 203-204 (2003) 836 | Yoshii, R., see Okabe, M. | 203-204 (2003) 714 |
| Yamamoto, Y., see Tomita, M. | 203-204 (2003) 465 | Yoshikawa, S., H. Morita, F. Toujou, T. Matsunaga and K. Tsukamoto, Steady-state surface concentration profiles of primary ion species during secondary ion mass spectrometry measurements | 203-204 (2003) 252 |
| Yamamoto, Y., Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo, Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect | 203-204 (2003) 863 | Yoshikawa, S., see Tsukamoto, K. | 203-204 (2003) 404 |
| Yamamura, Y., and M. Ishida, Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer | 203-204 (2003) 62 | Yuki, M., see Tadokoro, N. | 203-204 (2003) 72 |
| Yamamura, Y., see Muramoto, T. | 203-204 (2003) 143 | Yurimoto, H., K. Nagashima and T. Kunihiro, High precision isotope micro-imaging of materials | 203-204 (2003) 793 |
| Yamazaki, K., see Kataoka, Y. | 203-204 (2003) 43 | Zanderigo, F., D. Brazzelli, S. Rocca, A. Pregolato, A. Grossi and G. Queirolo, Gate oxide properties investigated by TOF-SIMS profiles on CMOS devices | 203-204 (2003) 437 |
| Yanagihara, K., see Hayashi, S. | 203-204 (2003) 339 | Zanderigo, F., see Bersani, M. | 203-204 (2003) 281 |
| Yanagihara, K., see Hayashi, S. | 203-204 (2003) 504 | Zhao, C., see Conard, T. | 203-204 (2003) 400 |
| Yang, M.H., see Schueler, B.W. | 203-204 (2003) 847 | Zhigilei, L.V., see Garrison, B.J. | 203-204 (2003) 67 |
| Yegles, M., see Audinot, J.-N. | 203-204 (2003) 718 | Zhu, L., and T. Liew, Spectral characterization of perfluoropolyethers lubricant irradiated by laser light | 203-204 (2003) 871 |
| Yeo, K.L., A.T.S. Wee, A. See, R. Liu and C.M. Ng, SIMS backside depth profiling of ultra shallow implants | 203-204 (2003) 335 | Zielinski, M., see Barcz, A. | 203-204 (2003) 396 |
| Yingling, Y.G., see Garrison, B.J. | 203-204 (2003) 67 | Zimmer, R., see Ruch, D. | 203-204 (2003) 566 |
| Yokokawa, H., see Horita, T. | 203-204 (2003) 634 | Zimmermann, U., see Linnarsson, M.K. | 203-204 (2003) 427 |
| Yoshida, A., see Miyaki, S. | 203-204 (2003) 836 | | |
| Yoshida, M., see Takanashi, K. | 203-204 (2003) 609 | | |



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Applied Surface Science 203–204 (2003) XVI–XXXIX

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Subject Index

Alkali metals

- Surface roughening of silicon under ultra-low-energy cesium bombardment, Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 43
- Ionization probability of atoms and molecules sputtered from a cesium covered silver surface, S. Meyer, C. Staudt and A. Wucher 203–204 (2003) 48
- Work function change caused by alkali ion sputtering, A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 203–204 (2003) 94
- Mass-resolved low-energy back-scattering of alkali ions, K. Franzreb and P. Williams 203–204 (2003) 98
- Effects of sample preparation on ion yield in the study of inorganic salts by s-SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203–204 (2003) 180

Alloys

- Energy distributions and excitation probability of nickel atoms sputtered from Ni₃Al, NiAl and Ni, M. Tan and B.V. King 203–204 (2003) 248
- Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys, A.A. Alibhai, R.J. Chater, D.S. McPhail and B.A. Shollock 203–204 (2003) 630
- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203–204 (2003) 660
- Application of high precision SIMS ²⁶Al–²⁶Mg analyses to the early solar system chronology, N.T. Kita, S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita 203–204 (2003) 806
- Oxidizing mechanism of beryllium–copper in alkaline solution, H. Kuroki and H. Kwarai 203–204 (2003) 867

Aluminium

- The unimolecular decay of Al_n[±] and Si_n[±] sputtered clusters, N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 203–204 (2003) 118
- Energy distributions and excitation probability of nickel atoms sputtered from Ni₃Al, NiAl and Ni, M. Tan and B.V. King 203–204 (2003) 248
- Comparison between Xe⁺ and O₂⁺ primary ions, at low impact energy, on B delta-doping, SiGe–Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203–204 (2003) 348
- Solubility limits of dopants in 4H–SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203–204 (2003) 427
- Application of high precision SIMS ²⁶Al–²⁶Mg analyses to the early solar system chronology, N.T. Kita, S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita 203–204 (2003) 806

Antimony

- Nanocrystals depth profiling by means of Cs⁺ in negative polarity with dual beam ToF-SIMS, M. Perego, S. Ferrari, S. Spiga and M. Fanciulli 203–204 (2003) 110
- Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams, Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 329

Argon

- B₄C/Mo/Si and Ta₂O₅/Ta nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354

Arsenic

- Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration, S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon 203-204 (2003) 302
- Characteristics of ultra-low-energy Cs⁺ ion beam bombardments, Z. Li, T. Hoshi and R. Oiwa 203-204 (2003) 323
- Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams, Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 203-204 (2003) 329
- Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis, M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Mura-koshi 203-204 (2003) 377

Atomic force microscopy

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203-204 (2003) 35
- Observation of ripple formation on O₂⁺-irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203-204 (2003) 152
- Dual ion beam analysis of boron implanted SiO₂/silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203-204 (2003) 409

Auger electron spectroscopy

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203-204 (2003) 35
- Dual ion beam analysis of boron implanted SiO₂/silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339

Beryllium

- Oxidizing mechanism of beryllium-copper in alkaline solution, H. Kuroki and H. Kawarai 203-204 (2003) 867

Biological materials

- Prospects for imaging TOF-SIMS: from fundamentals to biotechnology, N. Winograd 203-204 (2003) 13
- SIMS ion microscopy as a novel, practical tool for subcellular chemical imaging in cancer research, S. Chandra 203-204 (2003) 679
- Fine structures and ion images on fresh frozen dried ultrathin sections by transmission electron and scanning ion microscopy, K. Takaya, M. Okabe, M. Sawataishi, H. Takashima and T. Yoshida 203-204 (2003) 684
- Genome diagnostics with TOF-SIMS, H.F. Arlinghaus, M. Ostrop, O. Friedrichs and J.C. Feldner 203-204 (2003) 689
- ToF-SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions, C. Poleunis, C. Rubio, C. Compère and P. Bertrand 203-204 (2003) 693
- Characterization of adsorbed protein films using time-of-flight-secondary ion mass spectrometry and multivariate analysis, M.S. Wagner and D.G. Castner 203-204 (2003) 698
- Quantitative time-of-flight secondary ion mass spectrometry for the characterization of multicomponent adsorbed protein films, M.S. Wagner, M. Shen, T.A. Horbett and D.G. Castner 203-204 (2003) 704
- Detection of chlorinated pesticides on the surface of fungus using ToF-SIMS, B. Cliff, D.E. Weibel, N.P. Lockyer, H. Jungnickel, G. Stephens and J.C. Vickerman 203-204 (2003) 710
- Zinc detection in the islet of Langerhans by SIMS, M. Okabe, T. Yoshida, R. Yoshii, M. Sawataishi and K. Takaya 203-204 (2003) 714
- Detection and quantification of benzodiazepines in hair by ToF-SIMS: preliminary results, J.-N. Audinot, M. Yegles, A. Labarthe, D. Ruch, R. Wennig and H.-N. Migeon 203-204 (2003) 718
- TOF-SIMS investigation of the immobilization process of peptide nucleic acids, J.C. Feldner, M. Ostrop, O. Friedrichs, S. Sohn, D. Lipinsky, U. Gunst and H.F. Arlinghaus 203-204 (2003) 722
- Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS, M. Fartmann, S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus 203-204 (2003) 726
- Development of instrumentation for routine ToF-SIMS imaging analysis of biological material, B. Cliff, N.P. Lockyer, C. Corlett and J.C. Vickerman 203-204 (2003) 730

- Time-of-flight secondary ion mass spectrometry of fatty acids in rat retina, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 734
- Changes of vitamins A and E in the rat retina under light and dark conditions detected with TOF-SIMS, T. Amemiya, H. Gong, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 738
- Trace elements in lenses of normal Wistar Kyoto rats, A. Kinoshita, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 742
- Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of biosurfaces, S. Roberson, A. Sehgal, A. Fahey and A. Karim 203-204 (2003) 855
- TOF-SIMS characterization of planktonic foraminifera, G. Vering, C. Crone, J. Bijma and H.F. Arlinghaus 203-204 (2003) 785
- Boron**
- Evaluation of SIMS depth resolution using delta-doped multilayers and mixing-roughness-information depth model, A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 203-204 (2003) 294
- The features of using of BO_2^- secondary ions for SIMS depth profiling of shallow boron implantation in silicon, S.G. Simakin and V.K. Smirnov 203-204 (2003) 314
- Dual ion beam analysis of boron implanted SiO_2 /silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339
- $\text{B}_4\text{C}/\text{Mo}/\text{Si}$ and $\text{Ta}_2\text{O}_5/\text{Ta}$ nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203-204 (2003) 354
- Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for micro-electronics support applications, F. Jahnel and R. von Criegern 203-204 (2003) 367
- An (un)solvable problem in SIMS: B-interfacial profiling, W. Vandervorst, T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Frühauf, A. Bergmaier and G. Dollinger 203-204 (2003) 371
- Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis, M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi 203-204 (2003) 377
- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203-204 (2003) 427
- Quantitative analysis of the top 5 nm of boron ultra-shallow implants, J. Bellingham, M.G. Dowsett, E. Collart and D. Kirkwood 203-204 (2003) 851
- Boron silicon**
- SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams, S. Hayashi, A. Takano, H. Takenaka and Y. Homma 203-204 (2003) 298
- Carbides**
- $\text{B}_4\text{C}/\text{Mo}/\text{Si}$ and $\text{Ta}_2\text{O}_5/\text{Ta}$ nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203-204 (2003) 354
- Carbon**
- Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry, N. Tadokoro, M. Yuki and K. Osakabe 203-204 (2003) 72
- Ionization probability of sputtered cluster anions: C_n^- and Si_n^- and H. Gnaser 203-204 (2003) 78
- Development of a C_{60}^+ ion gun for static SIMS and chemical imaging, S.C.C. Wong, R. Hill, P. Blenkinsopp, N.P. Lockyer, D.E. Weibel and J.C. Vickerman 203-204 (2003) 219
- Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users, C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 203-204 (2003) 461
- SIMS depth profiling analysis of electrical arc residues in fire investigation, C.Y. Chen, Y.C. Ling, J.T. Wang and H.Y. Chen 203-204 (2003) 779
- Catalysis**
- Probing molecules on a surface by Cs^+ reactive ion scattering: identification of C_2H_x ($x \leq 4$) hydrocarbons, H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim 203-204 (2003) 842
- Cerium**
- Determination of proton and oxygen movements in solid oxides by the tracer gases exchange technique and secondary ion mass spectrometry, T. Horita,

- K. Yamaji, N. Sakai, Y. Xiong, T. Kato, H. Yokokawa and T. Kawada 203-204 (2003) 634
- Ceramics**
- Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling, P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 203-204 (2003) 639
- Chemical vapour deposition**
- Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition, I. Sakaguchi 203-204 (2003) 652
- Chlorine**
- Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users, C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 203-204 (2003) 461
- Chromium**
- Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203-204 (2003) 114
- Chromium carbon**
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203-204 (2003) 859
- Cluster**
- Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203-204 (2003) 114
- The unimolecular decay of Al_n^+ and Si_n^+ sputtered clusters, N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 203-204 (2003) 118
- MD simulation of cluster ejection due to sputtering by polyatomic projectiles, T. Muramoto and Y. Yamamura 203-204 (2003) 143
- Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface, M. Medvedeva, I. Wojciechowski and B.J. Garrison 203-204 (2003) 148
- Cation Mass Spectrometer: towards an optimisation of MCs_x^+ cluster analysis, T. Wirtz, H.-N. Migeon and H. Scherrer 203-204 (2003) 189
- Secondary ion mass spectrometry using cluster primary ion beams, G. Gillen and A. Fahey 203-204 (2003) 209
- Secondary ion mass spectrometry with gas cluster ion beams, N. Toyoda, J. Matsuo, T. Aoki, I. Yamada and D.B. Fenner 203-204 (2003) 214
- Cobalt**
- Elemental distribution analysis of positive electrode material for a nickel metal hydride battery, K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 203-204 (2003) 609
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203-204 (2003) 859
- Computer simulation**
- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203-204 (2003) 62
- Big molecule ejection—SIMS vs. MALDI, B.J. Garrison, A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd 203-204 (2003) 67
- Simulation of SiO_2 build-up in silicon under oxygen bombardment, B. Guzmán, J.J. Serrano, J.M. Blanco, M. Aguilar and O. Ameziane 203-204 (2003) 139
- MD simulation of cluster ejection due to sputtering by polyatomic projectiles, T. Muramoto and Y. Yamamura 203-204 (2003) 143
- Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation, A.V. Li-Fatou and M. Douglas 203-204 (2003) 290
- Copper**
- Copper drift in low dielectric constant insulator films caused by O_2^+ primary ion beam, K. Shibahara, D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa 203-204 (2003) 387
- Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users, C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 203-204 (2003) 461

- Oxidizing mechanism of beryllium-copper in alkaline solution, H. Kuroki and H. Kawarai 203-204 (2003) 867
- Corrosion**
- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203-204 (2003) 660
- Application of SIMS to silver tarnish at the British Museum, K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 203-204 (2003) 789
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203-204 (2003) 859
- Depth profiling**
- Depth profiling using ultra-low-energy secondary ion mass spectrometry, M.G. Dowsett 203-204 (2003) 5
- Apparent and real transient effects in SIMS depth profiling using oxygen bombardment, K. Wittmaack 203-204 (2003) 20
- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203-204 (2003) 62
- Secondary ion mass spectrometry using cluster primary ion beams, G. Gillen and A. Fahey 203-204 (2003) 209
- Surface roughening effect in sub-keV SIMS depth profiling, R. Liu, C.M. Ng and A.T.S. Wee 203-204 (2003) 256
- Accurate SIMS depth profiling for ultra-shallow implants using backside SIMS, C. Hongo, M. Tomita, M. Takenaka and A. Murakoshi 203-204 (2003) 264
- Detailed evaluation of the analytical resolution function, K. Wittmaack 203-204 (2003) 268
- On determining accurate positions, separations, and internal profiles for delta layers, M.G. Dowsett, J.H. Kelly, G. Rowlands, T.J. Ormsby, B. Guzmán, P. Augustus and R. Beanland 203-204 (2003) 273
- Low energy dual beam depth profiling: influence of sputter and analysis beam parameters on profile performance using TOF-SIMS, T. Grehl, R. Möllers and E. Niehuis 203-204 (2003) 277
- D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides, M. Bersani, D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo 203-204 (2003) 281
- Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation, A.V. Li-Fatou and M. Douglas 203-204 (2003) 290
- SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams, S. Hayashi, A. Takano, H. Takenaka and Y. Homma 203-204 (2003) 298
- Transient effects noted during Cs⁺ depth profile analysis of Si at high incidence angles, P.A.W. van der Heide and J. Bennett 203-204 (2003) 306
- The features of using of BO₂⁻ secondary ions for SIMS depth profiling of shallow boron implantation in silicon, S.G. Simakin and V.K. Smirnov 203-204 (2003) 314
- Six months repeatability of D-SIMS depth profile using an ultra-low-energy probe, Z. Li, T. Hoshi and R. Oiwa 203-204 (2003) 318
- Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams, Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 203-204 (2003) 329
- SIMS backside depth profiling of ultra shallow implants, K.L. Yeo, A.T.S. Wee, A. See, R. Liu and C.M. Ng 203-204 (2003) 335
- Dual ion beam analysis of boron implanted SiO₂/silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339
- Comparison between Xe⁺ and O₂⁺ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203-204 (2003) 348
- B₄C/Mo/Si and Ta₂O₅/Ta nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203-204 (2003) 354
- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203-204 (2003) 359
- Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for micro-electronics support applications, F. Jahnelt and R. von Criegern 203-204 (2003) 367
- An (un)solvable problem in SIMS: B-interfacial profiling, W. Vandervorst, T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Frühauf, A. Bergmaier and G. Dollinger 203-204 (2003) 371
- Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis, M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi 203-204 (2003) 377
- Copper drift in low dielectric constant insulator films caused by O₂⁺ primary ion beam, K. Shibahara, D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa 203-204 (2003) 387
- Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique, E. De

- Chambost, P. Monsallut, B. Rasser and M. Schuhmacher 203–204 (2003) 391
- Extremely deep SIMS profiling: oxygen in FZ silicon, A. Barcz, M. Zielinski, E. Nossarzewska and G. Lindstroem 203–204 (2003) 396
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondrean, C. Sparks, P.Y. Hung and A. Hou 203–204 (2003) 409
- Quantitative depth profiling of SiO_xN_y layers on Si, J.G.M. van Berkum, M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes 203–204 (2003) 414
- SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films, K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori 203–204 (2003) 418
- Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS, H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon 203–204 (2003) 423
- Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling, P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 203–204 (2003) 639
- Application of SIMS to the analysis of environmental samples, H. Seyama 203–204 (2003) 745
- SIMS depth profiling of working environment nanoparticles, P. Konarski, I. Iwanek and A. Mierzejewska 203–204 (2003) 757
- SIMS depth profiling analysis of electrical arc residues in fire investigation, C.Y. Chen, Y.C. Ling, J.T. Wang and H.Y. Chen 203–204 (2003) 779
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203–204 (2003) 859

Depth resolution

- Evaluation of SIMS depth resolution using delta-doped multilayers and mixing-roughness-information depth model, A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 203–204 (2003) 294

Doping effect

- Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration, S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon 203–204 (2003) 302
- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203–204 (2003) 427

- ToF-SIMS imaging of dopant diffusion in optical fibers, M. Hellsing, M. Fokine, A. Claesson, L.-E. Nilsson and W. Margulis 203–204 (2003) 648

Electron microscopy

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203–204 (2003) 35
- Surface roughening of silicon under ultra-low-energy cesium bombardment, Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 43
- Correction for the loss of depth resolution with accurate depth calibration when profiling with Cs^+ at angles of incidence above 50° to normal, J.H. Kelly, M.G. Dowsett, P. Augustus and R. Beanland 203–204 (2003) 260
- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203–204 (2003) 359
- Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS, H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon 203–204 (2003) 423
- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203–204 (2003) 427
- Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling, P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 203–204 (2003) 639
- Fine structures and ion images on fresh frozen dried ultrathin sections by transmission electron and scanning ion microscopy, K. Takaya, M. Okabe, M. Sawataishi, H. Takashima and T. Yoshida 203–204 (2003) 684
- Application of SIMS to silver tarnish at the British Museum, K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 203–204 (2003) 789
- Oxidizing mechanism of beryllium-copper in alkaline solution, H. Kuroki and H. Kawai 203–204 (2003) 867

Epitaxy

- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203–204 (2003) 427

Etching

- Development of a chemically assisted micro-beam etching system for three-dimensional microanalysis, Y. Tanaka, M. Karashima, K. Takanashi, T. Sakamoto, M. Owari and Y. Nihei 203–204 (2003) 205

Gallium

- Dynamic behavior of sputtering of implanted projectiles and target atoms under high fluence gallium ion bombardment, K. Ohya 203–204 (2003) 82

Gallium nitride

- Observation of ripple formation on O_2^+ -irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203–204 (2003) 152

Germanium

- Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 203–204 (2003) 56
- The energy spectra of secondary ions sputtered from Si and SiGe by ultra-low-energy primary ions, J. Bellingham and M.G. Dowsett 203–204 (2003) 130
- Transient processes and structural transformations in Si_xGe_{1-x} layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203–204 (2003) 285
- LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures, C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 203–204 (2003) 383
- Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique, E. De Chambost, P. Monsallut, B. Rasser and M. Schuhmacher 203–204 (2003) 391

Gold

- Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface, M. Medvedeva, I. Wojciechowski and B.J. Garrison 203–204 (2003) 148

- Prospects for imaging with TOF-SIMS using gold liquid metal ion sources, A.V. Walker and N. Winograd 203–204 (2003) 198
- Development and experimental application of a gold liquid metal ion source, N. Davies, D.E. Weibel, P. Blenkinsopp, N. Lockyer, R. Hill and J.C. Vickerman 203–204 (2003) 223

Halogens

- Electron transfer in ion interactions with chlorine covered silver surfaces, E.M. Staicu-Casagrande, L. Guillemot, S. Lacombe and V.A. Esaulov 203–204 (2003) 86
- SIMS depth profiling analysis of electrical arc residues in fire investigation, C.Y. Chen, Y.C. Ling, J.T. Wang and H.Y. Chen 203–204 (2003) 779
- Probing molecules on a surface by Cs^+ reactive ion scattering: identification of C_2H_x ($x \leq 4$) hydrocarbons, H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim 203–204 (2003) 842

Hafnium

- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203–204 (2003) 409

Hydrides

- Elemental distribution analysis of positive electrode material for a nickel metal hydride battery, K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 203–204 (2003) 609

Hydrocarbons

- ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates, Y. Abe and H. Okuhira 203–204 (2003) 175
- Probing molecules on a surface by Cs^+ reactive ion scattering: identification of C_2H_x ($x \leq 4$) hydrocarbons, H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim 203–204 (2003) 842
- Spectral characterization of perfluoropolyethers lubricant irradiated by laser light, L. Zhu and T. Liew 203–204 (2003) 871

Hydrogen

- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203–204 (2003) 427

- Hydrogen absorption of LaNi_5 after LiOD treatment and surface characterization by TOF-SIMS, C. Izawa, H.-H. Uchida, H. Okuhira and Y. Nishi 203-204 (2003) 665

Implantation

- SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams, S. Hayashi, A. Takano, H. Takenaka and Y. Homma 203-204 (2003) 298

Interfaces

- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203-204 (2003) 863

Ion bombardment

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203-204 (2003) 35
- Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O_2^+ bombardment, K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek 203-204 (2003) 39
- Surface roughening of silicon under ultra-low-energy cesium bombardment, Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 203-204 (2003) 43
- Dynamic behavior of sputtering of implanted projectiles and target atoms under high fluence gallium ion bombardment, K. Ohya 203-204 (2003) 82
- Electron transfer in ion interactions with chlorine covered silver surfaces, E.M. Staicu-Casagrande, L. Guillemot, S. Lacombe and V.A. Esaulov 203-204 (2003) 86
- Work function change caused by alkali ion sputtering, A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 203-204 (2003) 94
- The unimolecular decay of Al_n^+ and Si_n^+ sputtered clusters, N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 203-204 (2003) 118
- Observation of ripple formation on O_2^+ -irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203-204 (2003) 152
- Development of a chemically assisted micro-beam etching system for three-dimensional microanalysis, Y. Tanaka, M. Karashima, K. Takanashi, T. Sakamoto, M. Owari and Y. Nihei 203-204 (2003) 205

- Dual ion beam analysis of boron implanted SiO_2 /silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339

- Melt contribution to partitioning of trace element between plagioclase and basaltic magma of Fuji volcano, Japan, S. Togashi, N.T. Kita, A. Tomiya, Y. Morishita and N. Imai 203-204 (2003) 814

Ion implantation

- Transient processes and structural transformations in $\text{Si}_x\text{Ge}_{1-x}$ layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203-204 (2003) 285
- Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation, A.V. Li-Fatou and M. Douglas 203-204 (2003) 290
- Characteristics of ultra-low-energy Cs^+ ion beam bombardments, Z. Li, T. Hoshi and R. Oiwa 203-204 (2003) 323
- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203-204 (2003) 359
- Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis, M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi 203-204 (2003) 377
- Copper drift in low dielectric constant insulator films caused by O_2^+ primary ion beam, K. Shibahara, D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa 203-204 (2003) 387
- SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation, S. Hayashi, T. Sasaki, K. Kawamura, A. Matsumura, K. Yanagihara and K. Tanaka 203-204 (2003) 504
- Ion image enhancement using in-situ implantation of Cs^+ and O_2^+ ions, S. Seki, H. Tamura and W. Saitoh 203-204 (2003) 832
- Surface metal standards produced by ion implantation through a removable layer, B.W. Schueler, C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang 203-204 (2003) 847
- Quantitative analysis of the top 5 nm of boron ultra-shallow implants, J. Bellingham, M.G. Dowsett, E. Collart and D. Kirkwood 203-204 (2003) 851
- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203-204 (2003) 863
- Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry, Y. Lee, S. Han,

M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim

203-204 (2003) 875

Ion scattering

The dose dependence of Si sputtering with low energy ions in shallow depth profiling, D.W. Moon and H.I. Lee

203-204 (2003) 27

On the correlation between Si⁺ yields and surface oxygen concentration using in situ SIMS-LEIS, T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpennig and H.H. Brongersma

203-204 (2003) 30

Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O₂⁺ bombardment, K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek

203-204 (2003) 39

Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O₂⁺ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst

203-204 (2003) 56

Electron transfer in ion interactions with chlorine covered silver surfaces, E.M. Staicu-Casagrande, L. Guillemot, S. Lacombe and V.A. Esaulov

203-204 (2003) 86

Mass-resolved low-energy back-scattering of alkali ions, K. Franzreb and P. Williams

203-204 (2003) 98

Ionization probability changes of the Si⁺ ions during the transient for 3 keV O₂⁺ bombardment of Si, C. Huyghebaert, T. Janssens, B. Brijs and W. Vandervorst

203-204 (2003) 134

Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration, S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon

203-204 (2003) 302

Determination of the variation in sputter yield in the SIMS transient region using MEIS, M.G. Dowsett, T.J. Ormsby, F.S. Gard, S.H. Al-Harhi, B. Guzmán, C.F. McConville, T.C.Q. Noakes and P. Bailey

203-204 (2003) 363

TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard

203-204 (2003) 400

SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films, K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori

203-204 (2003) 418

Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS, H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon

203-204 (2003) 423

Probing molecules on a surface by Cs⁺ reactive ion scattering: identification of C₂H_x (x ≤ 4) hydrocarbons, H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim

203-204 (2003) 842

Iron

Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand

203-204 (2003) 114

Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett

203-204 (2003) 660

Lanthanides

SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias, S. Weber, S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt

203-204 (2003) 656

Laser processing

Estimation of useful yield in surface analysis using single photon ionisation, B.V. King, M.J. Pellin, J.F. Moore, I.V. Veryovkin, M.R. Savina and C.E. Tripa

203-204 (2003) 244

Spectral characterization of perfluoropolyethers lubricant irradiated by laser light, L. Zhu and T. Liew

203-204 (2003) 871

Lead

In situ U-Pb dating and REE analyses of phosphates in extraterrestrial materials, K. Terada and Y. Sano

203-204 (2003) 810

Lithium

Hydrogen absorption of LaNi₅ after LiOD treatment and surface characterization by TOF-SIMS, C. Izawa, H.-H. Uchida, H. Okuhira and Y. Nishi

203-204 (2003) 665

Magnesium

Application of high precision SIMS ²⁶Al - ²⁶Mg analyses to the early solar system chronology, N.T. Kita, S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita

203-204 (2003) 806

Mass spectrometry

- Cation Mass Spectrometer: towards an optimisation of MCs_x^+ cluster analysis, T. Wirtz, H.-N. Migeon and H. Scherrer 203–204 (2003) 189
- Trace element analysis of precious metals in minerals by time-of-flight resonance ionization mass spectrometry, S.S. Dimov and S.L. Chrysoulis 203–204 (2003) 235
- Spectral characterization of perfluoropolyethers lubricant irradiated by laser light, L. Zhu and T. Liew 203–204 (2003) 871

Metals

- Surface metal standards produced by ion implantation through a removable layer, B.W. Schueler, C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang 203–204 (2003) 847

Molecular dynamics

- Big molecule ejection—SIMS vs. MALDI, B.J. Garrison, A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd 203–204 (2003) 67
- MD simulation of cluster ejection due to sputtering by polyatomic projectiles, T. Muramoto and Y. Yamamura 203–204 (2003) 143
- Molecular SIMS for organic layers: new insights, P. Bertrand, A. Delcorte and B.J. Garrison 203–204 (2003) 160
- A microscopic view of organic sample sputtering, A. Delcorte, P. Bertrand and B.J. Garrison 203–204 (2003) 166
- Secondary ion mass spectrometry with gas cluster ion beams, N. Toyoda, J. Matsuo, T. Aoki, I. Yamada and D.B. Fenner 203–204 (2003) 214

Molybdenum

- $\text{B}_4\text{C}/\text{Mo}/\text{Si}$ and $\text{Ta}_2\text{O}_5/\text{Ta}$ nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354

Monte Carlo simulations

- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203–204 (2003) 62
- Dynamic behavior of sputtering of implanted projectiles and target atoms

- under high fluence gallium ion bombardment, K. Ohya 203–204 (2003) 82

Multilayers

- Evaluation of SIMS depth resolution using delta-doped multilayers and mixing-roughness-information depth model, A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 203–204 (2003) 294
- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe–Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203–204 (2003) 348

Nanostructures

- $\text{B}_4\text{C}/\text{Mo}/\text{Si}$ and $\text{Ta}_2\text{O}_5/\text{Ta}$ nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354
- LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures, C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 203–204 (2003) 383

Nickel

- Energy distributions and excitation probability of nickel atoms sputtered from Ni_3Al , NiAl and Ni , M. Tan and B.V. King 203–204 (2003) 248
- Elemental distribution analysis of positive electrode material for a nickel metal hydride battery, K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 203–204 (2003) 609
- Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys, A.A. Alibhai, R.J. Chater, D.S. McPhail and B.A. Shollock 203–204 (2003) 630

Nitrogen

- Determination of nitrogen in silicon carbide by secondary ion mass spectrometry, B. Ya Ber, D.Yu. Kazantsev, A.P. Kovarsky and R.R. Yafaev 203–204 (2003) 184

Nitrogen Auger electron spectroscopy

- Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition, I. Sakaguchi 203–204 (2003) 652

Nitrogen indium

- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203–204 (2003) 359

Optical properties

- ToF-SIMS imaging of dopant diffusion in optical fibers, M. Hellsing, M. Fokine, A. Claesson, L.-E. Nilsson and W. Margulis 203–204 (2003) 648

Organic substances

- Mechanism of metal cationization in organic SIMS, I. Wojciechowski, A. Delcorte, X. Gonze and P. Bertrand 203–204 (2003) 102
- Tribological characterisation of an organic coating by the use of ToF-SIMS, U. Bexell, P. Carlsson and M. Olsson 203–204 (2003) 596
- Characterization of methyl methacrylate oligomers using secondary ion mass spectrometry, APCI mass spectrometry and molecular orbital theory, T. Takeuchi, K. Iwai, K. Momoji, I. Miyamoto, K. Saiki and K. Hashimoto 203–204 (2003) 605
- Imaging TOF-SIMS for the surface analysis of silver halide microcrystals, J. Lenaerts, R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens 203–204 (2003) 614
- Fine structures and ion images on fresh frozen dried ultrathin sections by transmission electron and scanning ion microscopy, K. Takaya, M. Okabe, M. Sawataishi, H. Takashima and T. Yoshida 203–204 (2003) 684
- Analysis of condensation dusts from the heavy oil combustion using TOF-SIMS, S. Oishi, M. Shirahase, M. Sado and R. Oiwa 203–204 (2003) 772

Oxidation

- On the correlation between Si⁺ yields and surface oxygen concentration using in situ SIMS-LEIS, T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpennig and H.H. Brongersma 203–204 (2003) 30

- Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys, A.A. Alibhai, R.J. Chater, D.S. McPhail and B.A. Shollock 203–204 (2003) 630
- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203–204 (2003) 863
- Oxidizing mechanism of beryllium–copper in alkaline solution, H. Kuroki and H. Kawarai 203–204 (2003) 867

Oxides

- Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203–204 (2003) 114
- The features of using of BO₂[−] secondary ions for SIMS depth profiling of shallow boron implantation in silicon, S.G. Simakin and V.K. Smirnov 203–204 (2003) 314
- B₄C/Mo/Si and Ta₂O₅/Ta nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354
- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203–204 (2003) 400
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203–204 (2003) 409
- A study of defect structures in oxide materials by secondary ion mass spectrometry and H. Haneda 203–204 (2003) 625
- Determination of proton and oxygen movements in solid oxides by the tracer gases exchange technique and secondary ion mass spectrometry, T. Horita, K. Yamaji, N. Sakai, Y. Xiong, T. Kato, H. Yokokawa and T. Kawada 203–204 (2003) 634
- SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias, S. Weber, S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt 203–204 (2003) 656
- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203–204 (2003) 660

Oxygen

- Apparent and real transient effects in SIMS depth profiling using oxygen bombardment, K. Wittmaack 203–204 (2003) 20

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203-204 (2003) 35
- Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O_2^+ bombardment, K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek 203-204 (2003) 39
- Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 203-204 (2003) 56
- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203-204 (2003) 62
- Towards a model for the formation of positive Si^+ ions, T. Janssens, C. Huyghebaert and W. Vandervorst 203-204 (2003) 90
- Ionization probability changes of the Si^+ ions during the transient for 3 keV O_2^+ bombardment of Si, C. Huyghebaert, T. Janssens, B. Brijs and W. Vandervorst 203-204 (2003) 134
- Observation of ripple formation on O_2^+ -irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203-204 (2003) 152
- Transient processes and structural transformations in Si_xGe_{1-x} layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203-204 (2003) 285
- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holiger, J.C. Dupuy and N. Baboux 203-204 (2003) 348
- An (un)solvable problem in SIMS: B-interfacial profiling, W. Vandervorst, T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Frühauf, A. Bergmaier and G. Dollinger 203-204 (2003) 371
- Extremely deep SIMS profiling: oxygen in FZ silicon, A. Barcz, M. Zielinski, E. Nossarzewska and G. Lindstroem 203-204 (2003) 396
- SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation, S. Hayashi, T. Sasaki, K. Kawamura, A. Matsumura, K. Yanagihara and K. Tanaka 203-204 (2003) 504
- Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling, P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 203-204 (2003) 639
- Oxygen isotopic measurements on the Cameca Nanosims 50, G. Slodzian, F. Hillion, F.J. Stadermann and F. Horreard 203-204 (2003) 798
- Ion image enhancement using in-situ implantation of Cs^+ and O_2^+ ions, S. Seki, H. Tamura and W. Saitoh 203-204 (2003) 832
- ### Oxynitrides
- D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides, M. Bersani, D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo 203-204 (2003) 281
- Characteristics of ultra-low-energy Cs^+ ion beam bombardments, Z. Li, T. Hoshi and R. Oiwa 203-204 (2003) 323
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203-204 (2003) 409
- Quantitative depth profiling of SiO_xN_y layers on Si, J.G.M. van Berkum, M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes 203-204 (2003) 414
- SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films, K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori 203-204 (2003) 418
- Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS, H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon 203-204 (2003) 423
- ### Phosphoros
- TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material, A. Murase and T. Ohmori 203-204 (2003) 586
- ### Photo-electron spectroscopy
- Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry, N. Tadokoro, M. Yuki and K. Osakabe 203-204 (2003) 72
- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203-204 (2003) 400
- Time-of-flight-SIMS and XPS characterization of metal doped polymers, T.h. Gross, I. Retzko, J. Friedrich and W. Unger 203-204 (2003) 575

- Speciation of surface gold in pressure oxidized carbonaceous gold ores by TOF-SIMS and TOF-LIMS, S.S. Dimov, S.L. Chrysosoulis and R.N. Sodhi 203–204 (2003) 644
- ToF-SIMS and XPS characterisation of urban aerosols for pollution studies, P. Lazzeri, G. Clauser, E. Iacob, A. Lui, G. Tonidandel and M. Anderle 203–204 (2003) 767
- Application of SIMS to silver tarnish at the British Museum, K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 203–204 (2003) 789
- Plasma processing*
- Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry, Y. Lee, S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim 203–204 (2003) 875
- Platinum*
- Probing molecules on a surface by Cs⁺ reactive ion scattering: identification of C₂H_x (x ≤ 4) hydrocarbons, H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim 203–204 (2003) 842
- Polymer*
- The formation of singly and doubly cationized oligomers in SIMS, A. Delcorte, I. Wojciechowski, X. Gonze, B.J. Garrison and P. Bertrand 203–204 (2003) 106
- Molecular SIMS for organic layers: new insights, P. Bertrand, A. Delcorte and B.J. Garrison 203–204 (2003) 160
- A microscopic view of organic sample sputtering, A. Delcorte, P. Bertrand and B.J. Garrison 203–204 (2003) 166
- Rapid screening of molecular arrays using imaging TOF-SIMS, J.Y. Xu, R.M. Braun and N. Winograd 203–204 (2003) 201
- TOF-SIMS characterization of industrial materials: from silicon wafer to polymer, A. Karen, N. Man, T. Shibamori and K. Takahashi 203–204 (2003) 541
- Time-of-flight-SIMS and XPS characterization of metal doped polymers, T.H. Gross, I. Retzko, J. Friedrich and W. Unger 203–204 (2003) 575
- Insights into ToF-SIMS analysis of dendritic macromolecules: cationization and PCA to probe their molecular weight on surfaces, G. Coullerez, S. Lundmark, M. Malkoch, H. Magnusson, E. Malström, A. Hult and H.J. Mathieu 203–204 (2003) 620
- Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of biosurfaces, S. Roberson, A. Sehgal, A. Fahey and A. Karim 203–204 (2003) 855
- Spectral characterization of perfluoropolyethers lubricant irradiated by laser light, L. Zhu and T. Liew 203–204 (2003) 871
- Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry, Y. Lee, S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim 203–204 (2003) 875
- Radiation damage*
- Investigating the difficulty of eliminating flood gun damage in TOF-SIMS, I.S. Gilmore and M.P. Seah 203–204 (2003) 600
- Rare earth metals*
- In situ U–Pb dating and REE analyses of phosphates in extraterrestrial materials, K. Terada and Y. Sano 203–204 (2003) 810
- Secondary ion mass spectrometry*
- Depth profiling using ultra-low-energy secondary ion mass spectrometry, M.G. Dowsett 203–204 (2003) 5
- Prospects for imaging TOF-SIMS: from fundamentals to biotechnology, N. Winograd 203–204 (2003) 13
- Apparent and real transient effects in SIMS depth profiling using oxygen bombardment, K. Wittmaack 203–204 (2003) 20
- On the correlation between Si⁺ yields and surface oxygen concentration using in situ SIMS-LEIS, T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpennig and H.H. Brongersma 203–204 (2003) 30
- Ionization probability of atoms and molecules sputtered from a cesium covered silver surface, S. Meyer, C. Staudt and A. Wucher 203–204 (2003) 48
- Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs⁺ sputtering in negative mode by ToF-SIMS: a full spectrum approach, S. Ferrari, M. Perego and M. Fanciulli 203–204 (2003) 52
- Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O₂⁺ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 203–204 (2003) 56
- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203–204 (2003) 62

- Big molecule ejection—SIMS vs. MALDI, B.J. Garrison, A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd 203–204 (2003) 67
- Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry, N. Tadokoro, M. Yuki and K. Osakabe 203–204 (2003) 72
- Ionization probability of sputtered cluster anions: C_n^- and Si_n^- , H. Gnaser 203–204 (2003) 78
- Work function change caused by alkali ion sputtering, A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 203–204 (2003) 94
- Mechanism of metal cationization in organic SIMS, I. Wojciechowski, A. Delcorte, X. Gonze and P. Bertrand 203–204 (2003) 102
- The formation of singly and doubly cationized oligomers in SIMS, A. Delcorte, I. Wojciechowski, X. Gonze, B.J. Garrison and P. Bertrand 203–204 (2003) 106
- Nanocrystals depth profiling by means of Cs^+ in negative polarity with dual beam ToF-SIMS, M. Perego, S. Ferrari, S. Spiga and M. Fanciulli 203–204 (2003) 110
- Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203–204 (2003) 114
- Features of non-additive sputtering for various "molecular projectile—solid" systems, S.F. Belykh, A.P. Kovarsky, V.V. Palitsin, A. Adriaens and F. Adams 203–204 (2003) 122
- Effect of the projectile parameters on the charge state formation process in solid sputtering, S.F. Belykh, V.V. Palitsin, A. Adriaens and F. Adams 203–204 (2003) 126
- The energy spectra of secondary ions sputtered from Si and SiGe by ultra-low-energy primary ions, J. Bellingham and M.G. Dowsett 203–204 (2003) 130
- Ionization probability changes of the Si^+ ions during the transient for 3 keV O_2^+ bombardment of Si, C. Huyghebaert, T. Janssens, B. Brijs and W. Vandervorst 203–204 (2003) 134
- Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface, M. Medvedeva, I. Wojciechowski and B.J. Garrison 203–204 (2003) 148
- Observation of ripple formation on O_2^+ -irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203–204 (2003) 152
- Transient effects induced through ripple topography growth during Cs^+ depth profile analysis of Si at high incidence angles, P.A.W. van der Heide, M.S. Lim, S.S. Perry and J. Bennett 203–204 (2003) 156
- Molecular SIMS for organic layers: new insights, P. Bertrand, A. Delcorte and B.J. Garrison 203–204 (2003) 160
- A microscopic view of organic sample sputtering, A. Delcorte, P. Bertrand and B.J. Garrison 203–204 (2003) 166
- Ion-to-neutral conversion in time-of-flight secondary ion mass spectrometry, W. Szymczak and K. Wittmaack 203–204 (2003) 170
- ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates, Y. Abe and H. Okuhira 203–204 (2003) 175
- Effects of sample preparation on ion yield in the study of inorganic salts by s-SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203–204 (2003) 180
- Determination of nitrogen in silicon carbide by secondary ion mass spectrometry, B. Ya Ber, D.Yu. Kazantsev, A.P. Kovarsky and R.R. Yafaev 203–204 (2003) 184
- Prospects for imaging with TOF-SIMS using gold liquid metal ion sources, A.V. Walker and N. Winograd 203–204 (2003) 198
- Rapid screening of molecular arrays using imaging TOF-SIMS, J.Y. Xu, R.M. Braun and N. Winograd 203–204 (2003) 201
- Secondary ion mass spectrometry using cluster primary ion beams, G. Gillen and A. Fahey 203–204 (2003) 209
- Secondary ion mass spectrometry with gas cluster ion beams, N. Toyoda, J. Matsuo, T. Aoki, I. Yamada and D.B. Fenner 203–204 (2003) 214
- Development of a C_{60}^+ ion gun for static SIMS and chemical imaging, S.C.C. Wong, R. Hill, P. Blenkinsopp, N.P. Lockyer, D.E. Weibel and J.C. Vickerman 203–204 (2003) 219
- Development and experimental application of a gold liquid metal ion source, N. Davies, D.E. Weibel, P. Blenkinsopp, N. Lockyer, R. Hill and J.C. Vickerman 203–204 (2003) 223
- Nonresonant Laser-SNMS and TOF-SIMS analysis of sub- μm structures, F. Kollmer, N. Bourdos, R. Kamischke and A. Benninghoven 203–204 (2003) 238
- Estimation of useful yield in surface analysis using single photon ionisation, B.V. King, M.J. Pellin, J.F. Moore, I.V. Veryovkin, M.R. Savina and C.E. Tripa 203–204 (2003) 244
- Steady-state surface concentration profiles of primary ion species during secondary ion mass spectrometry measurements, S. Yoshikawa, H. Morita, F. Toujou, T. Matsunaga and K. Tsukamoto 203–204 (2003) 252
- Surface roughening effect in sub-keV SIMS depth profiling, R. Liu, C.M. Ng and A.T.S. Wee 203–204 (2003) 256
- Correction for the loss of depth resolution with accurate depth calibration when profiling with Cs^+ at angles of incidence

- above 50° to normal, J.H. Kelly, M.G. Dowsett, P. Augustus and R. Beanland 203–204 (2003) 260
- Accurate SIMS depth profiling for ultra-shallow implants using backside SIMS, C. Hongo, M. Tomita, M. Takenaka and A. Murakoshi 203–204 (2003) 264
- Detailed evaluation of the analytical resolution function, K. Wittmaack 203–204 (2003) 268
- On determining accurate positions, separations, and internal profiles for delta layers, M.G. Dowsett, J.H. Kelly, G. Rowlands, T.J. Ormsby, B. Guzmán, P. Augustus and R. Beanland 203–204 (2003) 273
- Low energy dual beam depth profiling: influence of sputter and analysis beam parameters on profile performance using TOF-SIMS, T. Grehl, R. Möllers and E. Niehuis 203–204 (2003) 277
- D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides, M. Bersani, D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo 203–204 (2003) 281
- Transient processes and structural transformations in $\text{Si}_x\text{Ge}_{1-x}$ layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203–204 (2003) 285
- Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation, A.V. Li-Fatou and M. Douglas 203–204 (2003) 290
- Evaluation of SIMS depth resolution using delta-doped multilayers and mixing-roughness-information depth model, A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 203–204 (2003) 294
- SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams, S. Hayashi, A. Takano, H. Takenaka and Y. Homma 203–204 (2003) 298
- Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration, S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon 203–204 (2003) 302
- Transient effects noted during Cs^+ depth profile analysis of Si at high incidence angles, P.A.W. van der Heide and J. Bennett 203–204 (2003) 306
- Using SIMS and the NIST standard reference material #2137 to calibrate standards used in the $^{11}\text{B}(\text{p}, \alpha)^8\text{Be}$ nuclear reaction analysis of B in Si, C.W. Magee and D.C. Jacobson 203–204 (2003) 310
- The features of using of BO_2^- secondary ions for SIMS depth profiling of shallow boron implantation in silicon, S.G. Simakin and V.K. Smirnov 203–204 (2003) 314
- Six months repeatability of D-SIMS depth profile using an ultra-low-energy probe, Z. Li, T. Hoshi and R. Oiwa 203–204 (2003) 318
- Characteristics of ultra-low-energy Cs^+ ion beam bombardments, Z. Li, T. Hoshi and R. Oiwa 203–204 (2003) 323
- Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams, Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 329
- SIMS backside depth profiling of ultra shallow implants, K.L. Yeo, A.T.S. Wee, A. See, R. Liu and C.M. Ng 203–204 (2003) 335
- Dual ion beam analysis of boron implanted $\text{SiO}_2/\text{silicon}$ interface, S. Hayashi and K. Yanagihara 203–204 (2003) 339
- A floating low energy electron gun (FLEG) for charge compensation in SIMS and other applications, R. Gibbons, M.G. Dowsett, J. Kelly, P. Blenkinsopp, R. Hill, D. Richards and N. Loibl 203–204 (2003) 343
- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203–204 (2003) 348
- $\text{B}_4\text{C}/\text{Mo}/\text{Si}$ and $\text{Ta}_2\text{O}_5/\text{Ta}$ nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354
- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203–204 (2003) 359
- Determination of the variation in sputter yield in the SIMS transient region using MEIS, M.G. Dowsett, T.J. Ormsby, F.S. Gard, S.H. Al-Harhi, B. Guzmán, C.F. McConville, T.C.Q. Noakes and P. Bailey 203–204 (2003) 363
- Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for microelectronics support applications, F. Jahnel and R. von Criegern 203–204 (2003) 367
- An (un)solvable problem in SIMS: B-interfacial profiling, W. Vandervorst, T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Frühauf, A. Bergmaier and G. Dollinger 203–204 (2003) 371
- Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis, M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi 203–204 (2003) 377
- LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures, C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 203–204 (2003) 383

- Copper drift in low dielectric constant insulator films caused by O_2^+ primary ion beam, K. Shibahara, D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa 203-204 (2003) 387
- Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique, E. De Chambost, P. Monsallut, B. Rasser and M. Schuhmacher 203-204 (2003) 391
- Extremely deep SIMS profiling: oxygen in FZ silicon, A. Barcz, M. Zielinski, E. Nossarzewska and G. Lindstroem 203-204 (2003) 396
- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203-204 (2003) 400
- Application of SIMS in microelectronics, K. Tsukamoto, S. Yoshikawa, F. Toujou and H. Morita 203-204 (2003) 404
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203-204 (2003) 409
- Quantitative depth profiling of SiO_xN_y layers on Si, J.G.M. van Berkum, M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes 203-204 (2003) 414
- SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films, K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori 203-204 (2003) 418
- Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS, H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon 203-204 (2003) 423
- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203-204 (2003) 427
- Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users, C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 203-204 (2003) 461
- SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation, S. Hayashi, T. Sasaki, K. Kawamura, A. Matsumura, K. Yanagihara and K. Tanaka 203-204 (2003) 504
- TOF-SIMS characterization of industrial materials: from silicon wafer to polymer, A. Karen, N. Man, T. Shibamori and K. Takahashi 203-204 (2003) 541
- Time-of-flight-SIMS and XPS characterization of metal doped polymers, T.h. Gross, I. Retzko, J. Friedrich and W. Unger 203-204 (2003) 575
- TOF-SIMS study of organosilane adsorption on model hydroxyl terminated surfaces, L. Houssiau and P. Bertrand 203-204 (2003) 580
- TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material, A. Murase and T. Ohmori 203-204 (2003) 586
- Characterization of lubricants for fluid dynamic bearing by TOF-SIMS, F. Toujou, K. Tsukamoto and K. Matsuoka 203-204 (2003) 590
- Tribological characterisation of an organic coating by the use of ToF-SIMS, U. Bexell, P. Carlsson and M. Olsson 203-204 (2003) 596
- Investigating the difficulty of eliminating flood gun damage in TOF-SIMS, I.S. Gilmore and M.P. Seah 203-204 (2003) 600
- Characterization of methyl methacrylate oligomers using secondary ion mass spectrometry, APCI mass spectrometry and molecular orbital theory, T. Takeuchi, K. Iwai, K. Momoji, I. Miyamoto, K. Saiki and K. Hashimoto 203-204 (2003) 605
- Elemental distribution analysis of positive electrode material for a nickel metal hydride battery, K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 203-204 (2003) 609
- Imaging TOF-SIMS for the surface analysis of silver halide microcrystals, J. Lenaerts, R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens 203-204 (2003) 614
- Insights into ToF-SIMS analysis of dendritic macromolecules: cationization and PCA to probe their molecular weight on surfaces, G. Coullerez, S. Lundmark, M. Malkoch, H. Magnusson, E. Malmström, A. Hult and H.J. Mathieu 203-204 (2003) 620
- A study of defect structures in oxide materials by secondary ion mass spectrometry and H. Haneda 203-204 (2003) 625
- Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys, A.A. Alibhai, R.J. Chater, D.S. McPhail and B.A. Shollock 203-204 (2003) 630
- Determination of proton and oxygen movements in solid oxides by the tracer gases exchange technique and secondary ion mass spectrometry, T. Horita, K. Yamaji, N. Sakai, Y. Xiong, T. Kato, H. Yokokawa and T. Kawada 203-204 (2003) 634
- Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling, P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 203-204 (2003) 639
- Speciation of surface gold in pressure oxidized carbonaceous gold ores by TOF-SIMS and TOF-LIMS, S.S. Dimov, S.L. Chrissoulis and R.N. Sodhi 203-204 (2003) 644

- ToF-SIMS imaging of dopant diffusion in optical fibers, M. Hellsing, M. Fokine, A. Claesson, L.-E. Nilsson and W. Margulis 203-204 (2003) 648
- Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition, I. Sakaguchi 203-204 (2003) 652
- SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias, S. Weber, S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt 203-204 (2003) 656
- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203-204 (2003) 660
- Hydrogen absorption of LaNi₅ after LiOD treatment and surface characterization by TOF-SIMS, C. Izawa, H.-H. Uchida, H. Okuhira and Y. Nishi 203-204 (2003) 665
- Chemical characterization of combustion deposits by TOF-SIMS, P. Sjövall, J. Lausmaa, C. Tullin and J. Högborg 203-204 (2003) 669
- A new shielded SIMS instrument for analysis of highly radioactive materials, B. Rasser, L. Desgranges and B. Pasquet 203-204 (2003) 673
- SIMS ion microscopy as a novel, practical tool for subcellular chemical imaging in cancer research and S. Chandra 203-204 (2003) 679
- Genome diagnostics with TOF-SIMS, H.F. Arlinghaus, M. Ostrop, O. Friedrichs and J.C. Feldner 203-204 (2003) 689
- ToF-SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions, C. Poleunis, C. Rubio, C. Compère and P. Bertrand 203-204 (2003) 693
- Characterization of adsorbed protein films using time-of-flight-secondary ion mass spectrometry and multivariate analysis, M.S. Wagner and D.G. Castner 203-204 (2003) 698
- Quantitative time-of-flight secondary ion mass spectrometry for the characterization of multicomponent adsorbed protein films, M.S. Wagner, M. Shen, T.A. Horbett and D.G. Castner 203-204 (2003) 704
- Detection of chlorinated pesticides on the surface of fungus using ToF-SIMS, B. Cliff, D.E. Weibel, N.P. Lockyer, H. Jungnickel, G. Stephens and J.C. Vickerman 203-204 (2003) 710
- Zinc detection in the islet of Langerhans by SIMS, M. Okabe, T. Yoshida, R. Yoshii, M. Sawataisi and K. Takaya 203-204 (2003) 714
- Detection and quantification of benzodiazepines in hair by ToF-SIMS: preliminary results, J.-N. Audinot, M. Yegles, A. Labarthe, D. Ruch, R. Wennig and H.-N. Migeon 203-204 (2003) 718
- TOF-SIMS investigation of the immobilization process of peptide nucleic acids, J.C. Feldner, M. Ostrop, O. Friedrichs, S. Sohn, D. Lipinsky, U. Gunst and H.F. Arlinghaus 203-204 (2003) 722
- Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS, M. Fartmann, S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus 203-204 (2003) 726
- Development of instrumentation for routine ToF-SIMS imaging analysis of biological material, B. Cliff, N.P. Lockyer, C. Corlett and J.C. Vickerman 203-204 (2003) 730
- Time-of-flight secondary ion mass spectrometry of fatty acids in rat retina, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 734
- Changes of vitamins A and E in the rat retina under light and dark conditions detected with TOF-SIMS, T. Amemiya, H. Gong, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 738
- Trace elements in lenses of normal Wistar Kyoto rats, A. Kinoshita, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 742
- Application of SIMS to the analysis of environmental samples and H. Seyama 203-204 (2003) 745
- Surface composition of atmospheric aerosol: individual particle characterization by TOF-SIMS, R.E. Peterson and B.J. Tyler 203-204 (2003) 751
- SIMS depth profiling of working environment nanoparticles, P. Konarski, I. Iwanek and A. Mierzejewska 203-204 (2003) 757
- Analysis of surface composition and internal structure of fly ash particles using an ion and electron multibeam microanalyzer, T. Sakamoto, K. Shibata, K. Takanashi, M. Owari and Y. Nihei 203-204 (2003) 762
- ToF-SIMS and XPS characterisation of urban aerosols for pollution studies, P. Lazzeri, G. Clauser, E. Iacob, A. Lui, G. Tonidandel and M. Anderle 203-204 (2003) 767
- Analysis of condensation dusts from the heavy oil combustion using TOF-SIMS, S. Oishi, M. Shirahase, M. Sado and R. Oiwa 203-204 (2003) 772
- TOF-SIMS measurements for toxic air pollutants adsorbed on the surface of airborne particles, B. Tomiyasu, T. Hoshi, M. Owari and Y. Nihei 203-204 (2003) 775
- SIMS depth profiling analysis of electrical arc residues in fire investigation, C.Y. Chen, Y.C. Ling, J.T. Wang and H.Y. Chen 203-204 (2003) 779
- TOF-SIMS characterization of planktonic foraminifera, G. Vering, C. Crone, J. Bijma and H.F. Arlinghaus 203-204 (2003) 785

- Application of SIMS to silver tarnish at the British Museum, K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 203-204 (2003) 789
- High precision isotope micro-imaging of materials, H. Yurimoto, K. Nagashima and T. Kunihiro 203-204 (2003) 793
- Oxygen isotopic measurements on the Cameca Nanosims 50, G. Slodzian, F. Hillion, F.J. Stadermann and F. Horreard 203-204 (2003) 798
- Silicon isotope fractionation during FZ growth of silicon crystals, Y. Morishita and H. Satoh 203-204 (2003) 802
- Application of high precision SIMS ^{26}Al - ^{26}Mg analyses to the early solar system chronology, N.T. Kita, S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita 203-204 (2003) 806
- In situ U-Pb dating and REE analyses of phosphates in extraterrestrial materials, K. Terada and Y. Sano 203-204 (2003) 810
- High resolution static SIMS imaging by time of flight SIMS, T. Hoshi and M. Kudo 203-204 (2003) 818
- Interpretation of TOF-SIMS images: multivariate and univariate approaches to image de-noising, image segmentation and compound identification, B. Tyler 203-204 (2003) 825
- Ion image enhancement using in-situ implantation of Cs^+ and O_2^+ ions, S. Seki, H. Tamura and W. Saitoh 203-204 (2003) 832
- Failure analysis of liquid crystal display panel by time-of-flight secondary ion mass spectrometry, S. Miyaki, A. Yoshida, Y. Yamamoto and K. Takeuchi 203-204 (2003) 836
- Surface metal standards produced by ion implantation through a removable layer, B.W. Schueler, C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang 203-204 (2003) 847
- Quantitative analysis of the top 5 nm of boron ultra-shallow implants, J. Belingham, M.G. Dowsett, E. Collart and D. Kirkwood 203-204 (2003) 851
- Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of biosurfaces, S. Roberson, A. Sehgal, A. Fahey and A. Karim 203-204 (2003) 855
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203-204 (2003) 859
- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203-204 (2003) 863
- Oxidizing mechanism of beryllium-copper in alkaline solution, H. Kuroki and H. Kawarai 203-204 (2003) 867

- Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry, Y. Lee, S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim 203-204 (2003) 875

Secondary neutral mass spectrometry

- A resonance photoionization sputtered neutral mass spectrometry instrument for submicron microarea analysis of ULSI devices, H. Shichi, S. Osabe, M. Sugaya, T. Ino, H. Kakibayashi, K. Kanehori and Y. Mitsui 203-204 (2003) 228
- Nonresonant Laser-SNMS and TOF-SIMS analysis of sub- μm structures, F. Kollmer, N. Bourdos, R. Kamischke and A. Benninghoven 203-204 (2003) 238
- Estimation of useful yield in surface analysis using single photon ionisation, B.V. King, M.J. Pellin, J.F. Moore, I.V. Veroyovkin, M.R. Savina and C.E. Tripa 203-204 (2003) 244
- Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS, M. Fartmann, S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus 203-204 (2003) 726

Semiconductors

- Application of SIMS in microelectronics, K. Tsukamoto, S. Yoshikawa, F. Toujou and H. Morita 203-204 (2003) 404

Silanes

- TOF-SIMS study of organosilane adsorption on model hydroxyl terminated surfaces, L. Houssiau and P. Bertrand 203-204 (2003) 580

Silicon

- The dose dependence of Si sputtering with low energy ions in shallow depth profiling, D.W. Moon and H.I. Lee 203-204 (2003) 27
- On the correlation between Si^+ yields and surface oxygen concentration using in situ SIMS-LEIS, T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpennig and H.H. Brongersma 203-204 (2003) 30
- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203-204 (2003) 35
- Doubly versus singly positively charged oxygen ions back-scattered from a

- silicon surface under dynamic O_2^+ bombardment, K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek 203–204 (2003) 39
- Surface roughening of silicon under ultra-low-energy cesium bombardment, Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 43
- Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs^+ sputtering in negative mode by ToF-SIMS: a full spectrum approach, S. Ferrari, M. Perego and M. Fanciulli 203–204 (2003) 52
- Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 203–204 (2003) 56
- Ionization probability of sputtered cluster anions: C_n^- and Si_n^- and H. Gnaser 203–204 (2003) 78
- Towards a model for the formation of positive Si^+ ions, T. Janssens, C. Huyghebaert and W. Vandervorst 203–204 (2003) 90
- The unimolecular decay of Al_n^+ and Si_n^+ sputtered clusters, N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 203–204 (2003) 118
- Effect of the projectile parameters on the charge state formation process in solid sputtering, S.F. Belykh, V.V. Palitsin, A. Adriaens and F. Adams 203–204 (2003) 126
- The energy spectra of secondary ions sputtered from Si and SiGe by ultra-low-energy primary ions, J. Bellingham and M.G. Dowsett 203–204 (2003) 130
- Ionization probability changes of the Si^+ ions during the transient for 3 keV O_2^+ bombardment of Si, C. Huyghebaert, T. Janssens, B. Brijs and W. Vandervorst 203–204 (2003) 134
- Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface, M. Medvedeva, I. Wojciechowski and B.J. Garrison 203–204 (2003) 148
- Transient effects induced through ripple topography growth during Cs^+ depth profile analysis of Si at high incidence angles, P.A.W. van der Heide, M.S. Lim, S.S. Perry and J. Bennett 203–204 (2003) 156
- Transient processes and structural transformations in Si_xGe_{1-x} layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203–204 (2003) 285
- Evaluation of SIMS depth resolution using delta-doped multilayers and mixing-roughness-information depth model, A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 203–204 (2003) 294
- Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration, S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon 203–204 (2003) 302
- Transient effects noted during Cs^+ depth profile analysis of Si at high incidence angles, P.A.W. van der Heide and J. Bennett 203–204 (2003) 306
- Characteristics of ultra-low-energy Cs^+ ion beam bombardments, Z. Li, T. Hoshi and R. Oiwa 203–204 (2003) 323
- Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams, Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 329
- Dual ion beam analysis of boron implanted SiO_2 /silicon interface, S. Hayashi and K. Yanagihara 203–204 (2003) 339
- $B_4C/Mo/Si$ and Ta_2O_5/Ta nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354
- Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for micro-electronics support applications, F. Jahnel and R. von Criegern 203–204 (2003) 367
- LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures, C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 203–204 (2003) 383
- Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique, E. De Chambost, P. Monsallut, B. Rasser and M. Schuhmacher 203–204 (2003) 391
- Extremely deep SIMS profiling: oxygen in FZ silicon, A. Barcz, M. Zielinski, E. Nossarzewska and G. Lindstroem 203–204 (2003) 396
- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203–204 (2003) 400
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203–204 (2003) 409
- Quantitative depth profiling of SiO_xN_y layers on Si, J.G.M. van Berkum, M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes 203–204 (2003) 414
- SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films, K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori 203–204 (2003) 418
- SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation, S. Hayashi, T. Sasaki, K. Kawamura, A.

- Matsumura, K. Yanagihara and K. Tanaka 203-204 (2003) 504
- TOF-SIMS characterization of industrial materials: from silicon wafer to polymer, A. Karen, N. Man, T. Shibamori and K. Takahashi 203-204 (2003) 541
- Oxygen isotopic measurements on the Cameca Nanosims 50, G. Slodzian, F. Hillion, F.J. Stadermann and F. Horreard 203-204 (2003) 798
- Silicon isotope fractionation during FZ growth of silicon crystals, Y. Morishita and H. Satoh 203-204 (2003) 802
- Quantitative analysis of the top 5 nm of boron ultra-shallow implants, J. Bellingham, M.G. Dowsett, E. Collart and D. Kirkwood 203-204 (2003) 851
- Silicon carbide*
- Determination of nitrogen in silicon carbide by secondary ion mass spectrometry, B. Ya Ber, D.Yu. Kazantsev, A.P. Kovarsky and R.R. Yafaev 203-204 (2003) 184
- Solubility limits of dopants in 4H-SiC, M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 203-204 (2003) 427
- Silicon germanium*
- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203-204 (2003) 348
- Silicon oxide*
- Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs^+ sputtering in negative mode by ToF-SIMS: a full spectrum approach, S. Ferrari, M. Perego and M. Fanciulli 203-204 (2003) 52
- Simulation of SiO_2 build-up in silicon under oxygen bombardment, B. Guzmán, J.J. Serrano, J.M. Blanco, M. Aguilar and O. Ameziane 203-204 (2003) 139
- Dual ion beam analysis of boron implanted SiO_2 /silicon interface, S. Hayashi and K. Yanagihara 203-204 (2003) 339
- Silver*
- Ionization probability of atoms and molecules sputtered from a cesium covered silver surface, S. Meyer, C. Staudt and A. Wucher 203-204 (2003) 48
- Electron transfer in ion interactions with chlorine covered silver surfaces, E.M. Staicu-Casagrande, L. Guillemot, S. Lacombe and V.A. Esaulov 203-204 (2003) 86
- ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates, Y. Abe and H. Okuhira 203-204 (2003) 175
- Imaging TOF-SIMS for the surface analysis of silver halide microcrystals, J. Lenaerts, R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens 203-204 (2003) 614
- Application of SIMS to silver tarnish at the British Museum, K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 203-204 (2003) 789
- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203-204 (2003) 863
- Sputtering*
- The dose dependence of Si sputtering with low energy ions in shallow depth profiling, D.W. Moon and H.I. Lee 203-204 (2003) 27
- Ionization probability of atoms and molecules sputtered from a cesium covered silver surface, S. Meyer, C. Staudt and A. Wucher 203-204 (2003) 48
- Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs^+ sputtering in negative mode by ToF-SIMS: a full spectrum approach, S. Ferrari, M. Perego and M. Fanciulli 203-204 (2003) 52
- Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe, C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 203-204 (2003) 56
- Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer, Y. Yamamura and M. Ishida 203-204 (2003) 62
- Ionization probability of sputtered cluster anions: C_n^- and Si_n^- and H. Gnaser 203-204 (2003) 78
- Dynamic behavior of sputtering of implanted projectiles and target atoms under high fluence gallium ion bombardment, K. Ohya 203-204 (2003) 82
- Work function change caused by alkali ion sputtering, A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 203-204 (2003) 94
- The unimolecular decay of Al_n^+ and Si_n^+ sputtered clusters, N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 203-204 (2003) 118
- Features of non-additive sputtering for various "molecular projectile-solid"

- systems, S.F. Belykh, A.P. Kovarsky, V.V. Palitsin, A. Adriaens and F. Adams 203–204 (2003) 122
- Effect of the projectile parameters on the charge state formation process in solid sputtering, S.F. Belykh, V.V. Palitsin, A. Adriaens and F. Adams 203–204 (2003) 126
- Simulation of SiO₂ build-up in silicon under oxygen bombardment, B. Guzmán, J.J. Serrano, J.M. Blanco, M. Aguilar and O. Ameziane 203–204 (2003) 139
- MD simulation of cluster ejection due to sputtering by polyatomic projectiles, T. Muramoto and Y. Yamamura 203–204 (2003) 143
- Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface, M. Medvedeva, I. Wojciechowski and B.J. Garrison 203–204 (2003) 148
- A microscopic view of organic sample sputtering, A. Delcorte, P. Bertrand and B.J. Garrison 203–204 (2003) 166
- Energy distributions and excitation probability of nickel atoms sputtered from Ni₃Al, NiAl and Ni, M. Tan and B.V. King 203–204 (2003) 248
- Transient processes and structural transformations in Si_xGe_{1-x} layers during oxygen implantation and sputtering, D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 203–204 (2003) 285
- Determination of the variation in sputter yield in the SIMS transient region using MEIS, M.G. Dowsett, T.J. Ormsby, F.S. Gard, S.H. Al-Harthi, B. Guzmán, C.F. McConville, T.C.Q. Noakes and P. Bailey 203–204 (2003) 363

Steel

- Tribological characterisation of an organic coating by the use of ToF-SIMS, U. Bexell, P. Carlsson and M. Olsson 203–204 (2003) 596
- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203–204 (2003) 660
- ToF-SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions, C. Poleunis, C. Rubio, C. Compère and P. Bertrand 203–204 (2003) 693

Sulfur

- Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users, C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 203–204 (2003) 461

Superlattices

- Comparison between Xe⁺ and O₂⁺ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holiger, J.C. Dupuy and N. Baboux 203–204 (2003) 348

Surface roughness

- Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model, Y. Homma, A. Takano and Y. Higashi 203–204 (2003) 35
- Surface roughening of silicon under ultra-low-energy cesium bombardment, Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 203–204 (2003) 43
- Observation of ripple formation on O₂⁺-irradiated GaN surfaces using atomic force microscopy, M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 203–204 (2003) 152
- Surface roughening effect in sub-keV SIMS depth profiling, R. Liu, C.M. Ng and A.T.S. Wee 203–204 (2003) 256

Surface structure

- Low energy SIMS characterisation of ultra thin oxides on ferrous alloys, E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 203–204 (2003) 660

Tantalum

- B₄C/Mo/Si and Ta₂O₅/Ta nanostructures analysed by ultra-low energy argon ion beams, P. Konarski and A. Mierzejewska 203–204 (2003) 354

Thin films

- Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition and I. Sakaguchi 203–204 (2003) 652

Time-of-flight techniques

- Prospects for imaging TOF-SIMS: from fundamentals to biotechnology and N. Winograd 203–204 (2003) 13
- Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs⁺ sputtering in negative mode by

- ToF-SIMS: a full spectrum approach, S. Ferrari, M. Perego and M. Fanciulli 203-204 (2003) 52
- Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry, N. Tadokoro, M. Yuki and K. Osakabe 203-204 (2003) 72
- Nanocrystals depth profiling by means of Cs^+ in negative polarity with dual beam ToF-SIMS, M. Perego, S. Ferrari, S. Spiga and M. Fanciulli 203-204 (2003) 110
- Molecular SIMS for organic layers: new insights, P. Bertrand, A. Delcorte and B.J. Garrison 203-204 (2003) 160
- Ion-to-neutral conversion in time-of-flight secondary ion mass spectrometry, W. Szymczak and K. Wittmaack 203-204 (2003) 170
- ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates, Y. Abe and H. Okuhira 203-204 (2003) 175
- Prospects for imaging with TOF-SIMS using gold liquid metal ion sources, A.V. Walker and N. Winograd 203-204 (2003) 198
- Rapid screening of molecular arrays using imaging TOF-SIMS, J.Y. Xu, R.M. Braun and N. Winograd 203-204 (2003) 201
- Trace element analysis of precious metals in minerals by time-of-flight resonance ionization mass spectrometry, S.S. Dimov and S.L. Chrysoulis 203-204 (2003) 235
- Nonresonant Laser-SNMS and TOF-SIMS analysis of sub- μm structures, F. Kollmer, N. Bourdos, R. Kamischke and A. Benninghoven 203-204 (2003) 238
- Low energy dual beam depth profiling: influence of sputter and analysis beam parameters on profile performance using TOF-SIMS, T. Grehl, R. Möllers and E. Niehuis 203-204 (2003) 277
- D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides, M. Bersani, D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo 203-204 (2003) 281
- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203-204 (2003) 400
- TOF-SIMS characterization of industrial materials: from silicon wafer to polymer, A. Karen, N. Man, T. Shibamori and K. Takahashi 203-204 (2003) 541
- Time-of-flight-SIMS and XPS characterization of metal doped polymers, T.h. Gross, I. Retzko, J. Friedrich and W. Unger 203-204 (2003) 575
- TOF-SIMS study of organosilane adsorption on model hydroxyl terminated surfaces, L. Houssiau and P. Bertrand 203-204 (2003) 580
- TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material, A. Murase and T. Ohmori 203-204 (2003) 586
- Characterization of lubricants for fluid dynamic bearing by TOF-SIMS, F. Toudjou, K. Tsukamoto and K. Matsuoka 203-204 (2003) 590
- Tribological characterisation of an organic coating by the use of ToF-SIMS, U. Bexell, P. Carlsson and M. Olsson 203-204 (2003) 596
- Investigating the difficulty of eliminating flood gun damage in TOF-SIMS, I.S. Gilmore and M.P. Seah 203-204 (2003) 600
- Elemental distribution analysis of positive electrode material for a nickel metal hydride battery, K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 203-204 (2003) 609
- Imaging TOF-SIMS for the surface analysis of silver halide microcrystals, J. Lenaerts, R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens 203-204 (2003) 614
- Insights into ToF-SIMS analysis of dendritic macromolecules: cationization and PCA to probe their molecular weight on surfaces, G. Coullerez, S. Lundmark, M. Malkoch, H. Magnusson, E. Malmström, A. Hult and H.J. Mathieu 203-204 (2003) 620
- Speciation of surface gold in pressure oxidized carbonaceous gold ores by TOF-SIMS and TOF-LIMS, S.S. Dimov, S.L. Chrysoulis and R.N. Sodhi 203-204 (2003) 644
- ToF-SIMS imaging of dopant diffusion in optical fibers, M. Hellsing, M. Fokine, A. Claesson, L.-E. Nilsson and W. Margulis 203-204 (2003) 648
- Hydrogen absorption of LaNi_5 after LiOD treatment and surface characterization by TOF-SIMS, C. Izawa, H.-H. Uchida, H. Okuhira and Y. Nishi 203-204 (2003) 665
- Chemical characterization of combustion deposits by TOF-SIMS, P. Sjövall, J. Lausmaa, C. Tullin and J. Högberg 203-204 (2003) 669
- Genome diagnostics with TOF-SIMS, H.F. Arlinghaus, M. Ostrop, O. Friedrichs and J.C. Feldner 203-204 (2003) 689
- ToF-SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions, C. Poleunis, C. Rubio, C. Compère and P. Bertrand 203-204 (2003) 693
- Characterization of adsorbed protein films using time-of-flight-secondary ion mass spectrometry and multivariate analysis, M.S. Wagner and D.G. Castner 203-204 (2003) 698
- Quantitative time-of-flight secondary ion mass spectrometry for the characterization of multicomponent adsorbed protein films, M.S. Wagner, M. Shen, T.A. Horbett and D.G. Castner 203-204 (2003) 704

- Detection of chlorinated pesticides on the surface of fungus using ToF-SIMS, B. Cliff, D.E. Weibel, N.P. Lockyer, H. Jungnickel, G. Stephens and J.C. Vickerman 203-204 (2003) 710
- Detection and quantification of benzodiazepines in hair by ToF-SIMS: preliminary results, J.-N. Audinot, M. Yegles, A. Labarthe, D. Ruch, R. Wennig and H.-N. Migeon 203-204 (2003) 718
- TOF-SIMS investigation of the immobilization process of peptide nucleic acids, J.C. Feldner, M. Ostrop, O. Friedrichs, S. Sohn, D. Lipinsky, U. Gunst and H.F. Arlinghaus 203-204 (2003) 722
- Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS, M. Fartmann, S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus 203-204 (2003) 726
- Development of instrumentation for routine ToF-SIMS imaging analysis of biological material, B. Cliff, N.P. Lockyer, C. Corlett and J.C. Vickerman 203-204 (2003) 730
- Time-of-flight secondary ion mass spectrometry of fatty acids in rat retina, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 734
- Changes of vitamins A and E in the rat retina under light and dark conditions detected with TOF-SIMS, T. Amemiya, H. Gong, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 738
- Trace elements in lenses of normal Wistar Kyoto rats, A. Kinoshita, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 203-204 (2003) 742
- Surface composition of atmospheric aerosol: individual particle characterization by TOF-SIMS, R.E. Peterson and B.J. Tyler 203-204 (2003) 751
- Analysis of surface composition and internal structure of fly ash particles using an ion and electron multibeam microanalyzer, T. Sakamoto, K. Shibata, K. Takanashi, M. Owari and Y. Nihei 203-204 (2003) 762
- ToF-SIMS and XPS characterisation of urban aerosols for pollution studies, P. Lazzeri, G. Clauser, E. Iacob, A. Lui, G. Tonidandel and M. Anderle 203-204 (2003) 767
- Analysis of condensation dusts from the heavy oil combustion using TOF-SIMS, S. Oishi, M. Shirahase, M. Sado and R. Oiwa 203-204 (2003) 772
- TOF-SIMS measurements for toxic air pollutants adsorbed on the surface of airborne particles, B. Tomiyasu, T. Hoshi, M. Owari and Y. Nihei 203-204 (2003) 775
- TOF-SIMS characterization of planktonic foraminifera, G. Vering, C. Crone, J. Bijma and H.F. Arlinghaus 203-204 (2003) 785
- High resolution static SIMS imaging by time of flight SIMS, T. Hoshi and M. Kudo 203-204 (2003) 818
- Interpretation of TOF-SIMS images: multivariate and univariate approaches to image de-noising, image segmentation and compound identification, B. Tyler 203-204 (2003) 825
- Failure analysis of liquid crystal display panel by time-of-flight secondary ion mass spectrometry, S. Miyaki, A. Yoshida, Y. Yamamoto and K. Takeuchi 203-204 (2003) 836
- Surface metal standards produced by ion implantation through a removable layer, B.W. Schueler, C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang 203-204 (2003) 847
- Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of biosurfaces, S. Roberson, A. Sehgal, A. Fahey and A. Karim 203-204 (2003) 855
- Estimation of ToF-SIMS information depth in micro-corrosion analysis, Y. Abe, M. Komatsu and H. Okuhira 203-204 (2003) 859
- Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry, Y. Lee, S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim 203-204 (2003) 875
- ### Titanium
- Investigation of the cluster ion formation process for inorganic compounds in static SIMS, F. Aubriet, C. Poleunis and P. Bertrand 203-204 (2003) 114
- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Hollier, J.C. Dupuy and N. Baboux 203-204 (2003) 348
- ### Tribology
- TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material, A. Murase and T. Ohmori 203-204 (2003) 586
- Characterization of lubricants for fluid dynamic bearing by TOF-SIMS, F. Toudjou, K. Tsukamoto and K. Matsuoka 203-204 (2003) 590
- Tribological characterisation of an organic coating by the use of ToF-SIMS, U. Bexell, P. Carlsson and M. Olsson 203-204 (2003) 596

Uranium

- In situ U-Pb dating and REE analyses of phosphates in extraterrestrial materials, K. Terada and Y. Sano 203-204 (2003) 810

Work function

- Ionization probability of sputtered cluster anions: C_n^- and Si_n^- and H. Gnaser 203-204 (2003) 78
- Work function change caused by alkali ion sputtering, A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 203-204 (2003) 94

Xenon

- Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe-Si superlattice and Al/Ti multilayer structures, F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 203-204 (2003) 348

X-ray spectroscopy

- LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures, C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 203-204 (2003) 383

Yttrium

- SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias, S. Weber, S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt 203-204 (2003) 656

Zinc

- Zinc detection in the islet of Langerhans by SIMS, M. Okabe, T. Yoshida, R. Yoshii, M. Sawataisi and K. Takaya 203-204 (2003) 714

Zinc oxide

- SIMS depth profiling of N and In in a ZnO single crystal, D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 203-204 (2003) 359
- A study of defect structures in oxide materials by secondary ion mass spectrometry and H. Haneda 203-204 (2003) 625
- Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition and I. Sakaguchi 203-204 (2003) 652
- Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect, Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 203-204 (2003) 863

Zirconium

- TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films, T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 203-204 (2003) 400
- SIMS depth profiling of advanced gate dielectric materials, J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 203-204 (2003) 409
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